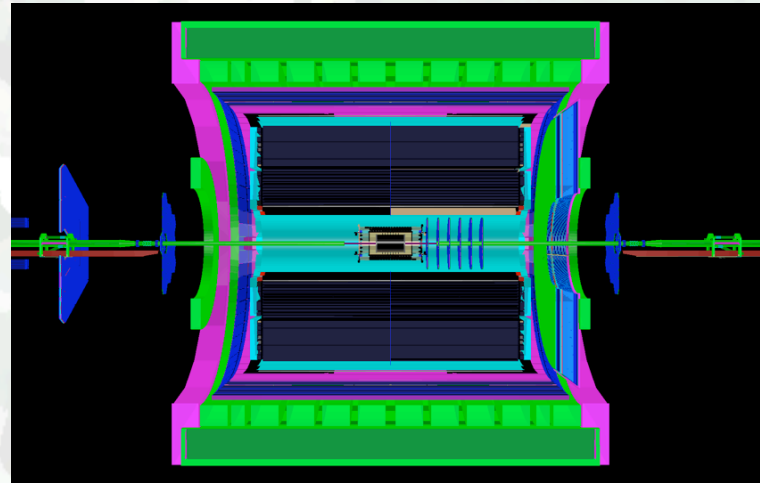


# The STAR Forward GEM Tracker (FGT)

Bernd Surröw

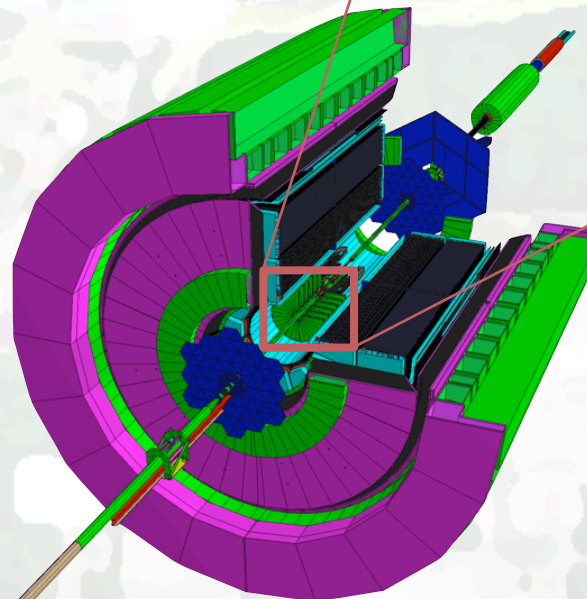
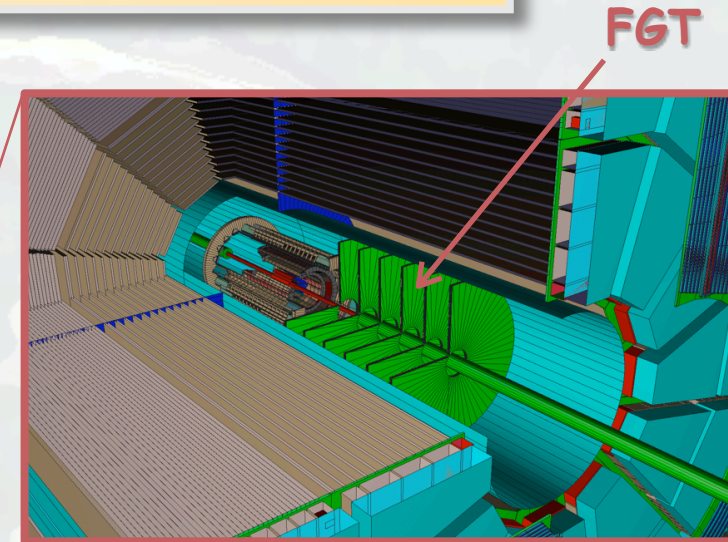


Massachusetts  
Institute of  
Technology



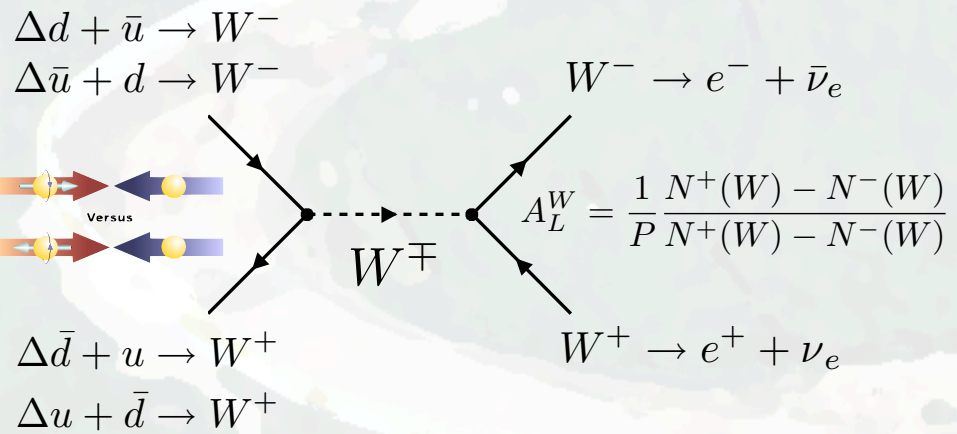
# Outline

- Physics motivation -  $W$  program in polarized pp collisions at RHIC
- **FGT** Layout
- **FGT** Technical Realization
  - Triple-GEM detector development - R&D
  - Mechanical design
  - Front-End Electronics
  - DAQ
- Summary

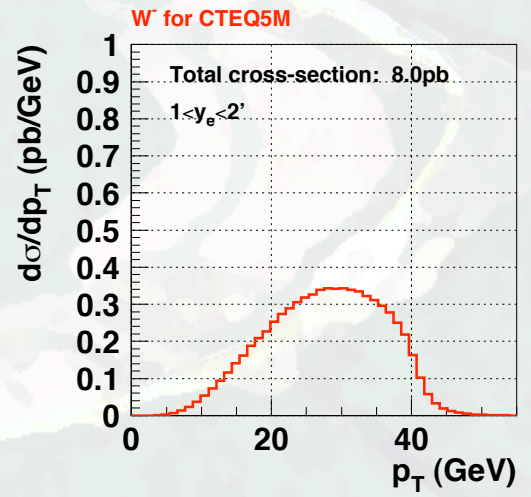
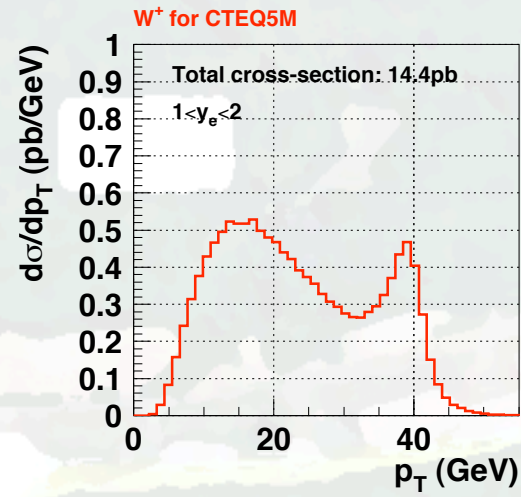


# FGT Physics motivation - W program

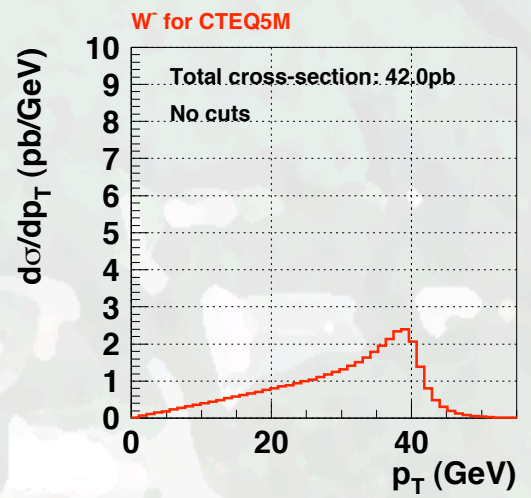
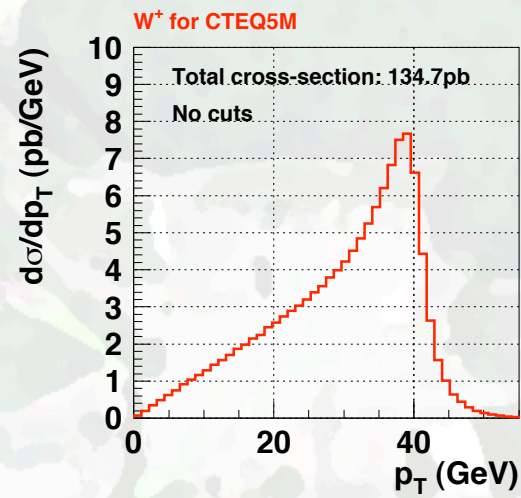
## □ Quark / Anti-Quark Polarization - W production



RHICBOS W simulation at 500GeV CME

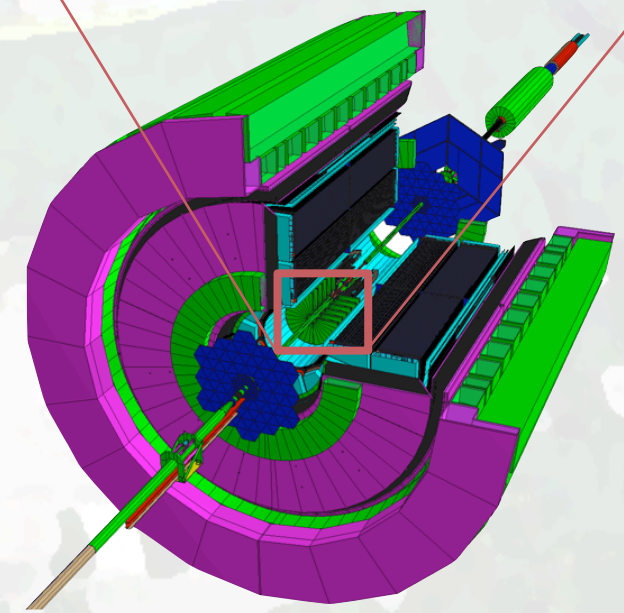
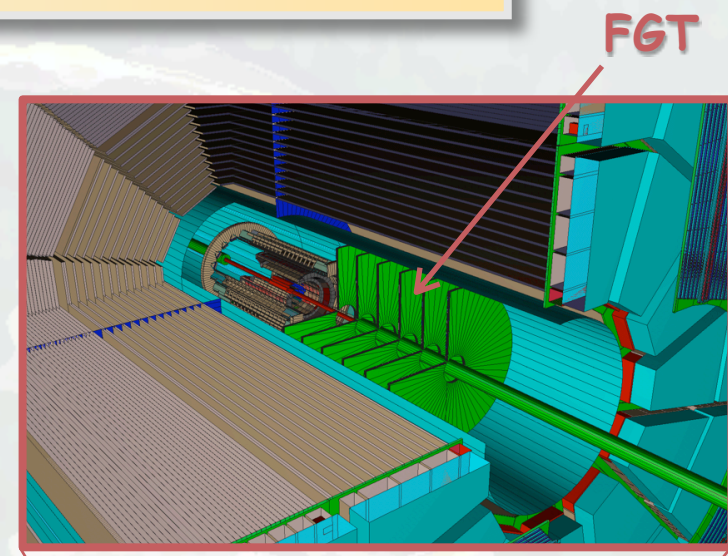
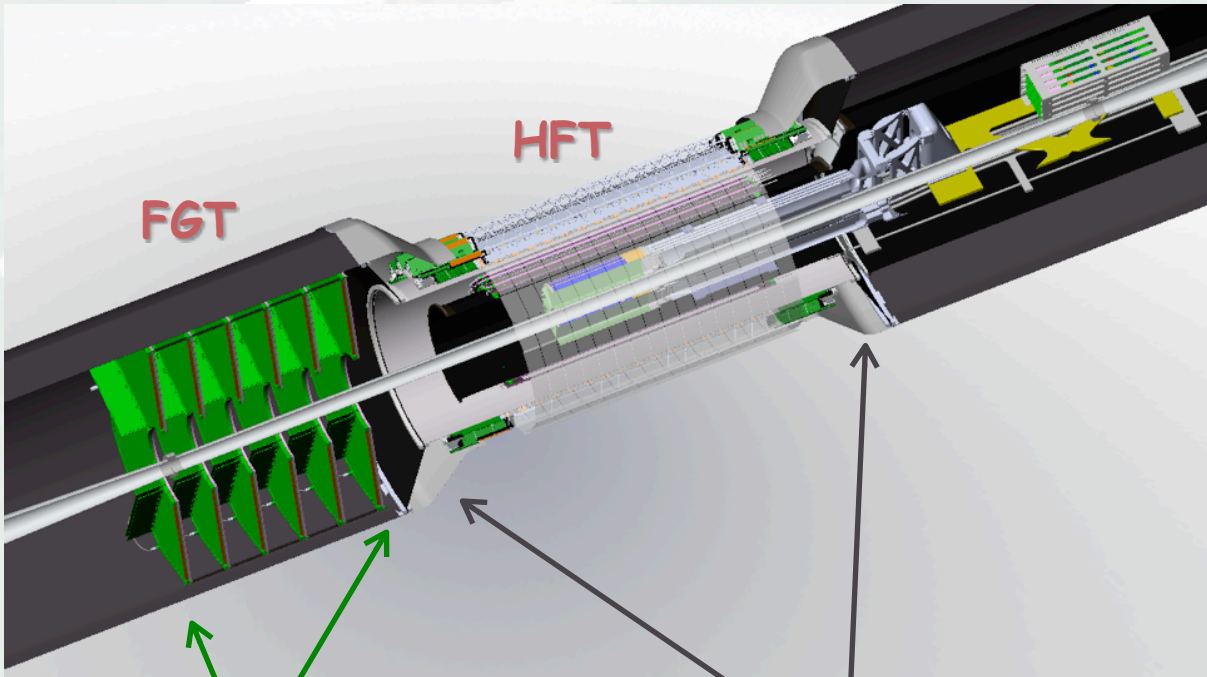


- **Key signature:** High p<sub>T</sub> lepton (e<sup>-</sup>/e<sup>+</sup> or μ<sup>-</sup>/μ<sup>+</sup>) (Max. M<sub>W</sub>/2) - Selection of W<sup>-</sup>/W<sup>+</sup>: Charge sign discrimination of high p<sub>T</sub> lepton
- **Required:** Lepton/Hadron discrimination



# FGT Layout

## Layout



- FGT: 6 light-weight triple-GEM disks - WEST side of STAR

- New mechanical support structure (STAR West / East)



# FGT Technical realization

## □ SBIR proposal (1)

### ○ SBIR: Small Business Innovation Research: US Government (DOE) funded program

- ☑ Phase I: Explore feasibility of innovative concepts with award of up to \$100k
- ☑ Phase II: Principal R&D effort with award of up to \$750k
- Phase III: Commercial application

### ○ SBIR: Collaborative effort of Tech-Etch Inc. with BNL, MIT and Yale University - Production of GEM foils

- Develop optimized production process for small (10cm X 10cm) and larger GEM foils
- Investigate a variety of materials
- Study post production handling: Cleaning, surface treatment and storage

### ○ New SBIR proposal: 2D readout board using chemical etching : Recently approved!

# FGT Technical realization

## □ SBIR proposal (2)

### ○ Tech-Etch Inc.: Company profile

- Manufacturer of precision flexible circuits
- Extensive experience in etching of copper traces and polyamide
- Strong ties to BNL, MIT and Yale University

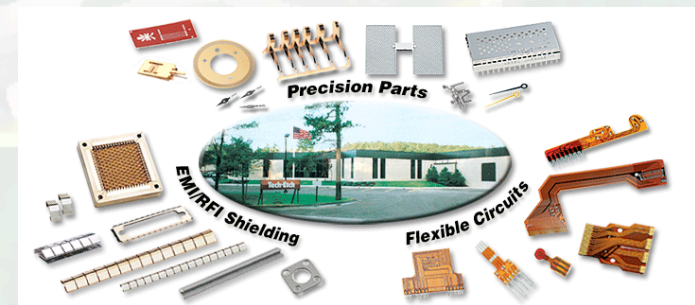
### ○ Critical performance parameters

- Achievable gain, gain uniformity and gain stability
- Energy resolution

### ○ Status

- Phase I / II approved - Dedicated production facility at Tech-Etch Inc.
- Success with 10cm X 10cm samples / First large GEM foils received

Tech-Etch Inc.



<http://www.tech-etch.com>



# FGT Technical realization

## □ R&D Development at MIT

### ○ Resources

- 2 dedicated clean rooms (Class ~1000) (MIT Bates Laboratory / MIT Laboratory for Nuclear Science)
- HV radioactive source setup / HV box / Light-microscope / Laminar flow hood / GEM foil CCD camera scanner

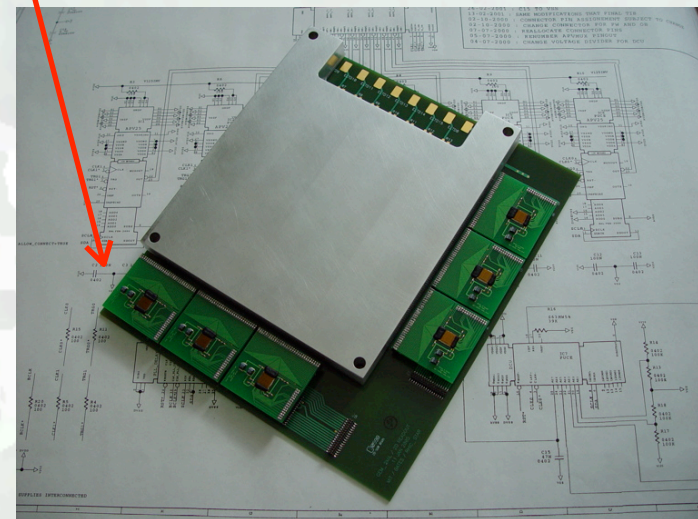
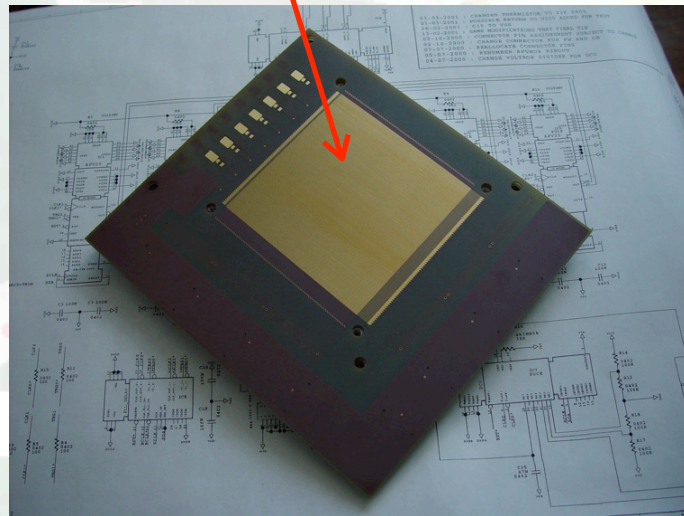
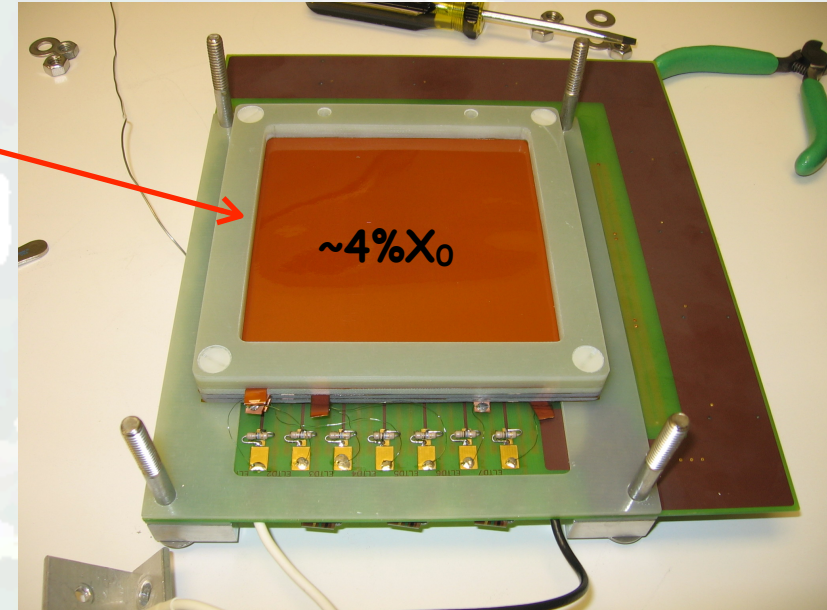
### ○ R&D Activities so far based on 10cm X 10cm samples

- Dark current / resistivity tests
- Optical scans
- Sources tests and test beam experiment at FNAL

○ **Publications:** 1) U. Becker et al., NIM A556 527 (2006). 2) F. Simon et al., IEEE Trans. Nucl. Sci. 54, 2646 (2007). 3) F. Simon et al., NIM A598 432 (2009).

# FGT Technical realization

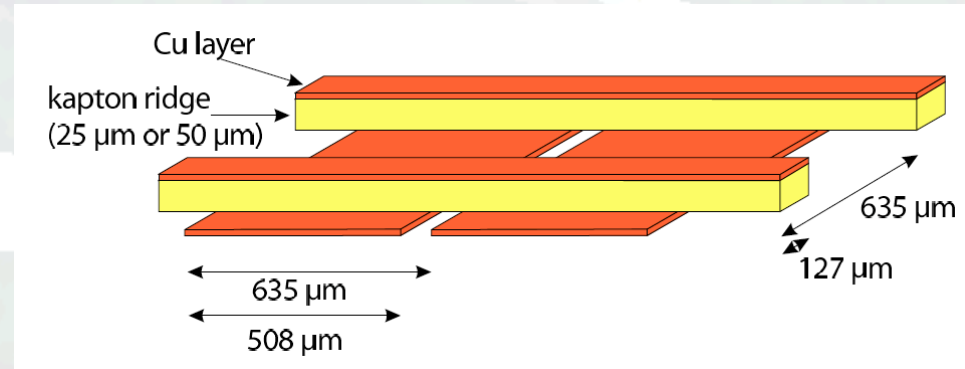
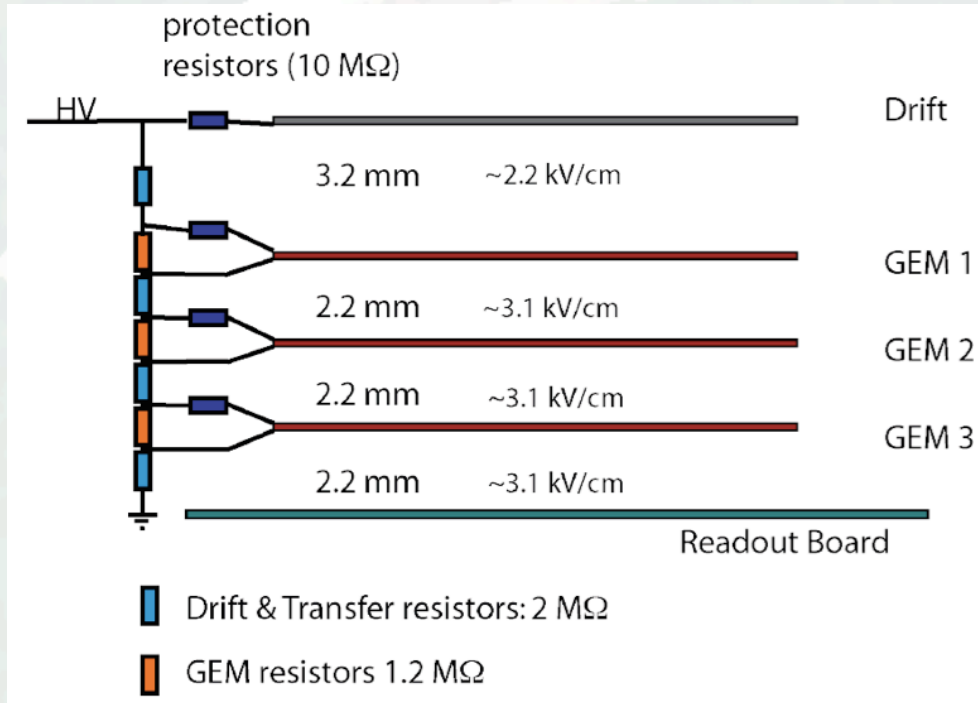
- Prototype triple-GEM configuration (1)
  - Prototype triple-GEM detector (Ar/CO<sub>2</sub> 70:30 gas-mixture) to allow flexible handling
  - Integrated APV25-S1 chip readout system
  - 2D projective readout board, using laser etching and micro-machining





# FGT Technical realization

## □ Prototype triple-GEM configuration (2)



- Test beam operating voltage: ~3750V-3800V corresponding to ~385V-395V per GEM foil

- Testbeam effective gain:  $\sim 3.5 \cdot 10^3$  ( $\sim 2.5 \cdot 10^4$  bench tests)

- Laser etched 2D readout board (Compunetics Inc.)

- Test beam configuration:

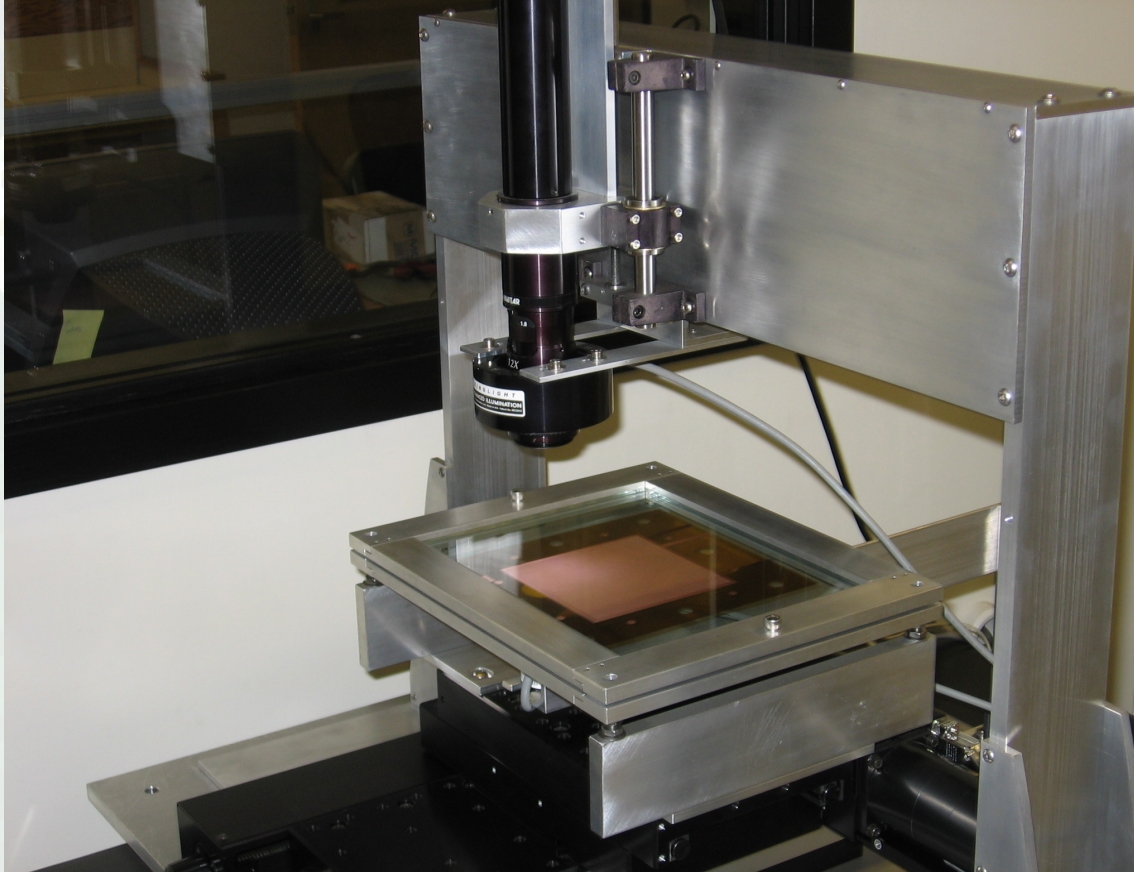
Top strips (Y):  $\sim 127 \mu\text{m}$

Bottom strips (X):  $508 \mu\text{m}$

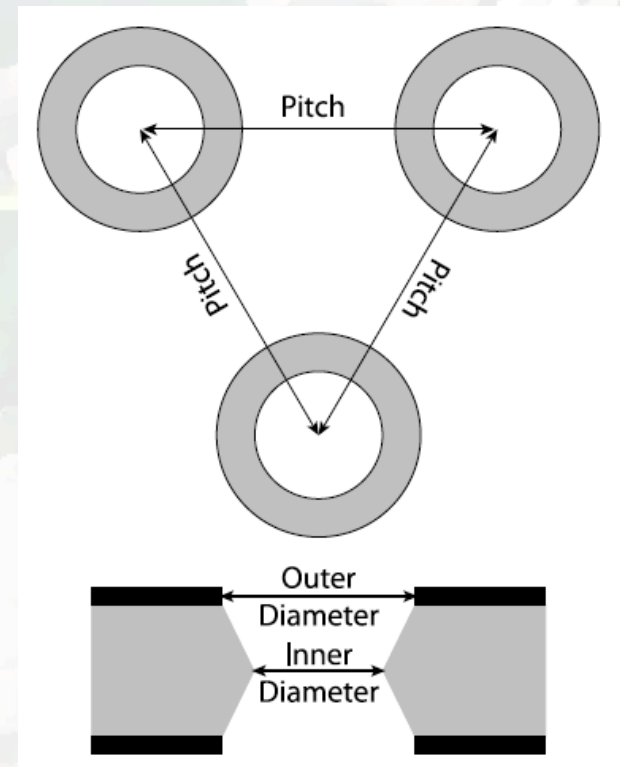
- Two separations:  $25 \mu\text{m}$  and  $50 \mu\text{m}$

# FGT Technical realization

## □ Optical scans (1)



- 2D scanning table with CCD camera - fully automated
- Scan GEM foils to measure hole diameter (inner and outer) and pitch



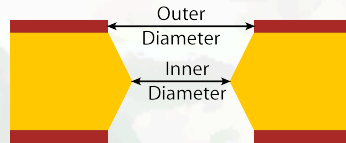
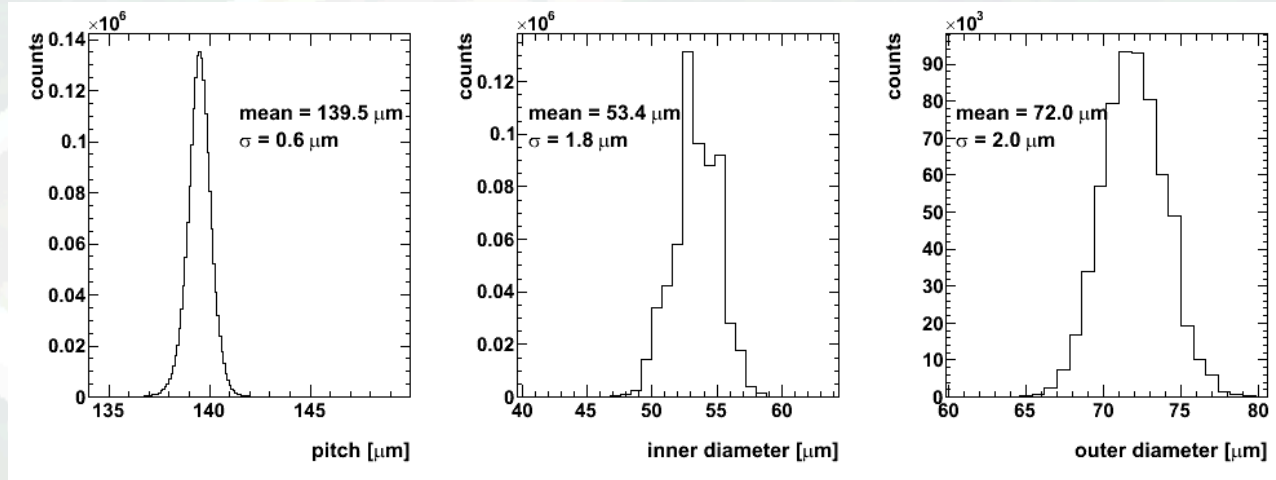
## ○ Check for defects:

- Missing holes, enlarged holes, dirt in holes and etching defects

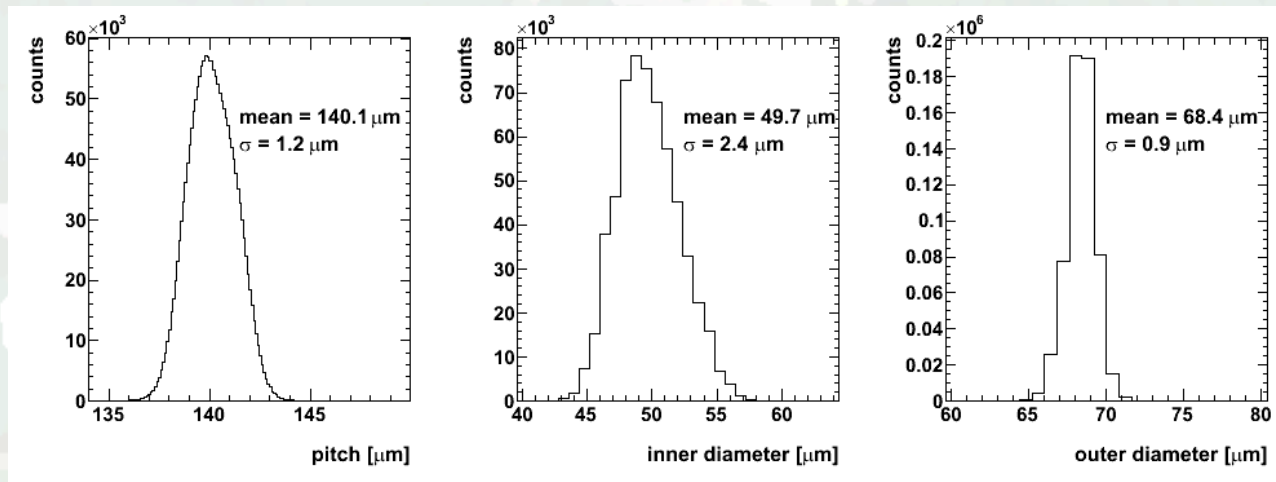
# FGT Technical realization

## □ Optical scans (2)

Tech-Etch



CERN

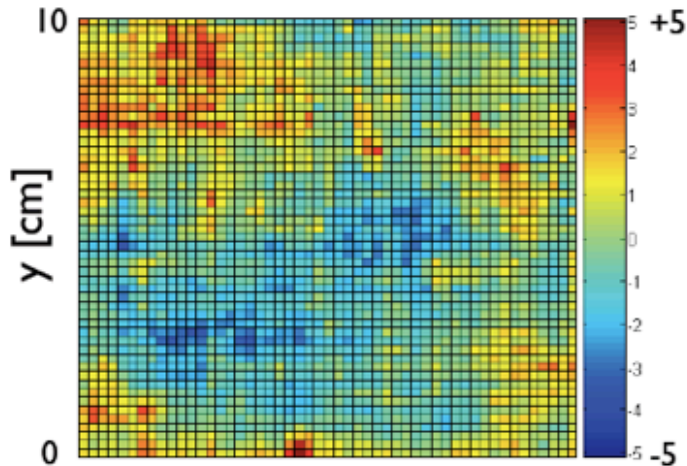


- Geometrical parameters are similar for Tech-Etch and CERN foils (10cm X 10cm samples)

# FGT Technical realization

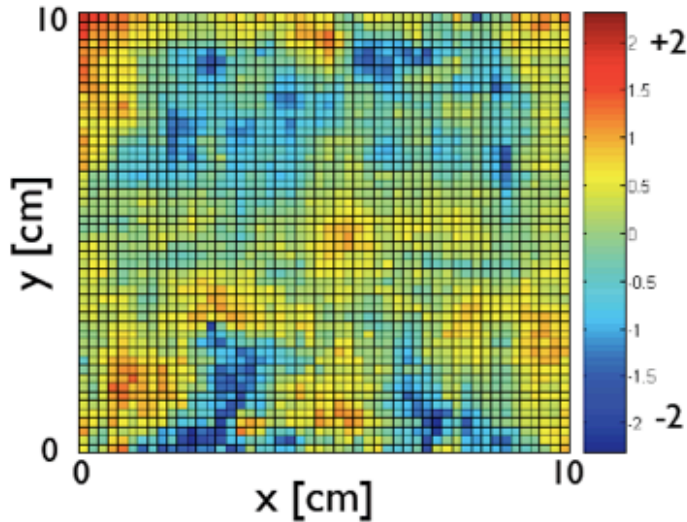
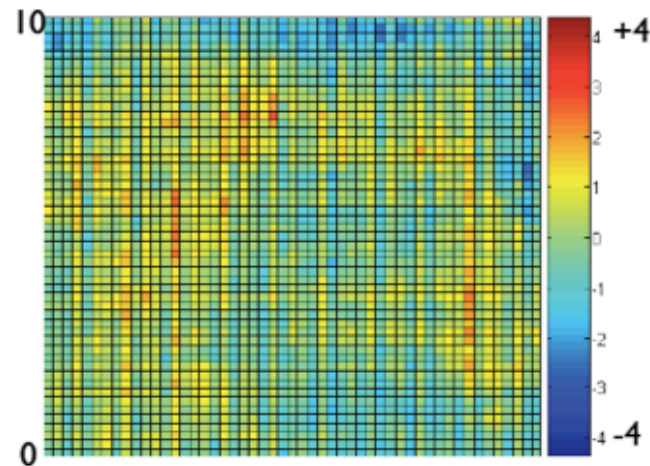
## □ Optical scans (3)

outer holes

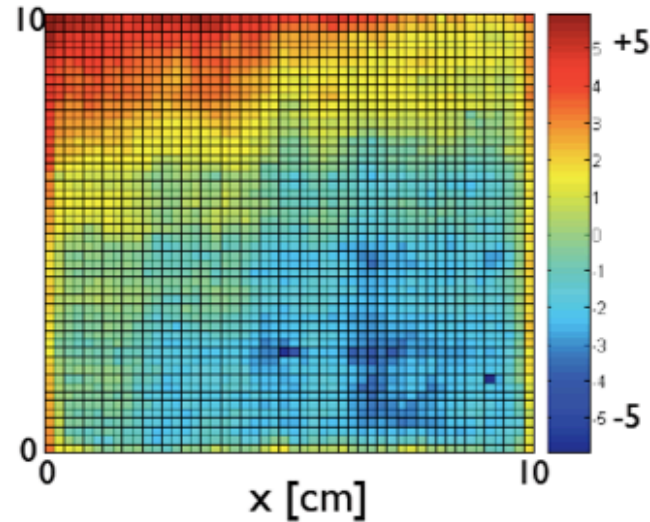


Tech-Etch

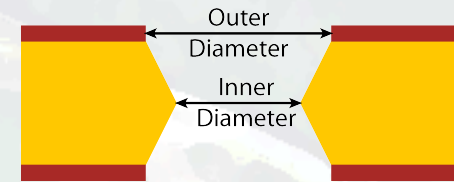
inner holes



CERN



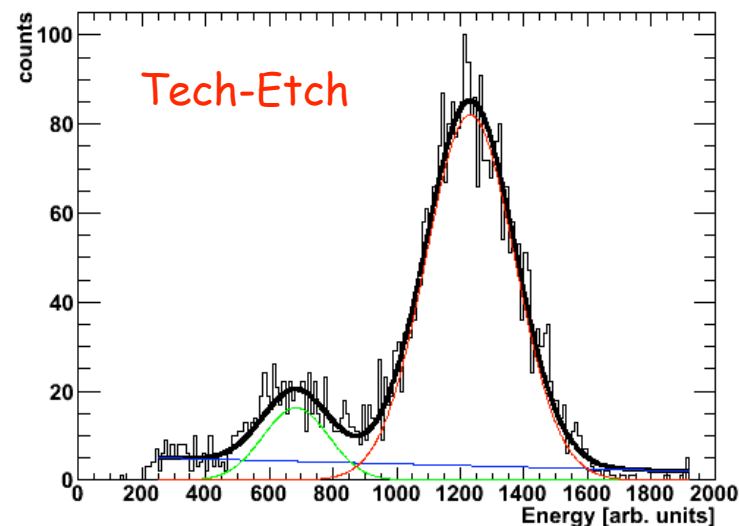
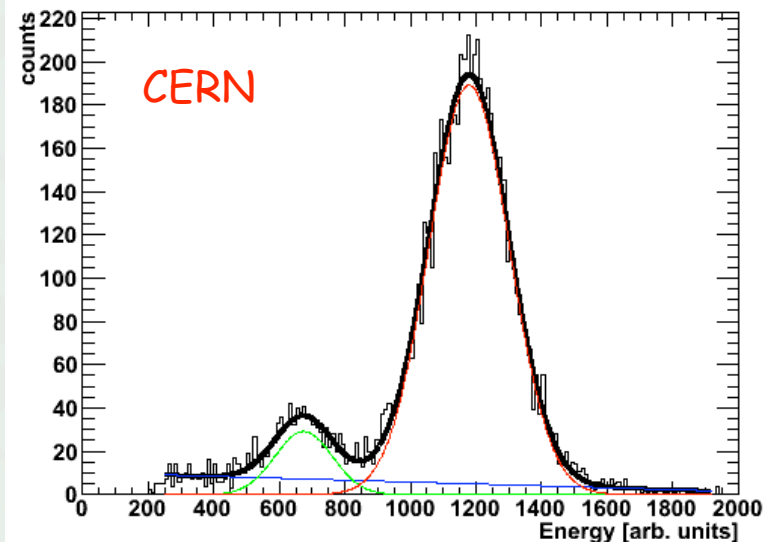
deviation from mean [μm]



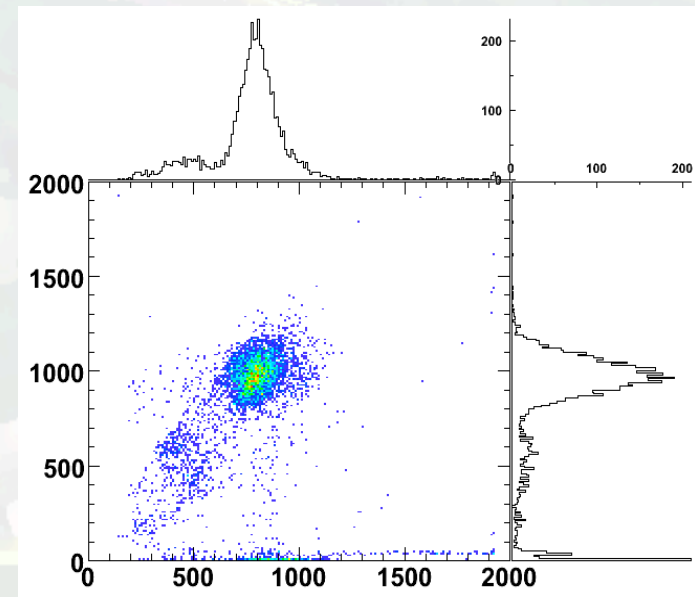
- Uniformity of outer/inner hole diameters for Tech-Etch and CERN foils (10cm X 10cm samples)

# FGT Technical realization

- Source tests (1)
  - Two identical detectors, one with CERN foils, one using Tech-Etch foils
  - Both detectors give reasonable X-Ray spectrum using  $^{55}\text{Fe}$  source with comparable energy resolution ( $\sim 20\%$ )

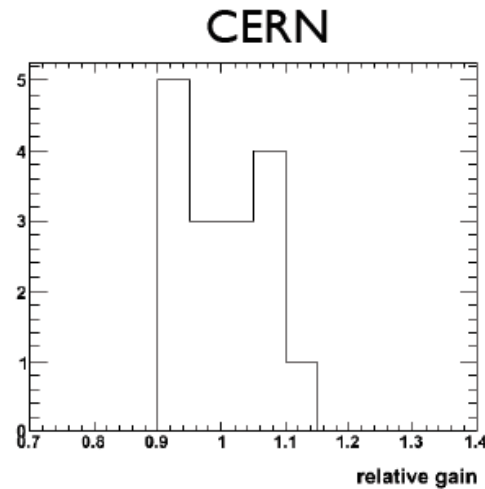
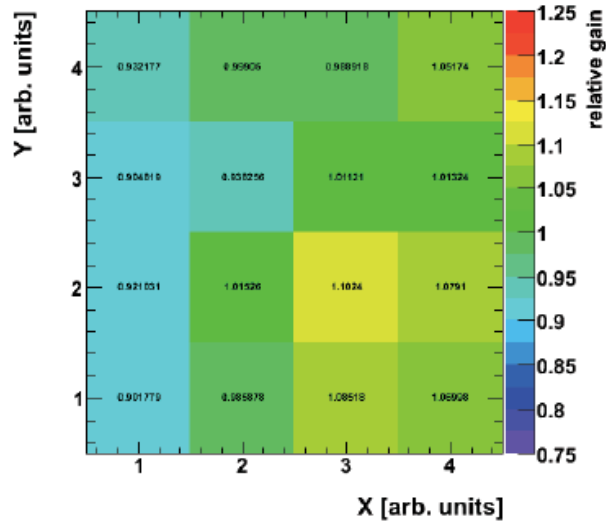


Correlation  
of X-Y  
readout  
plane

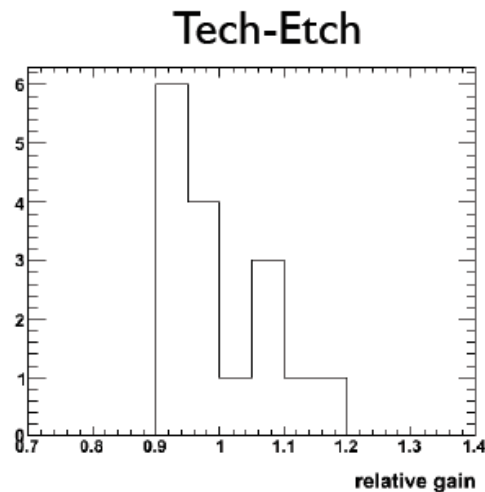
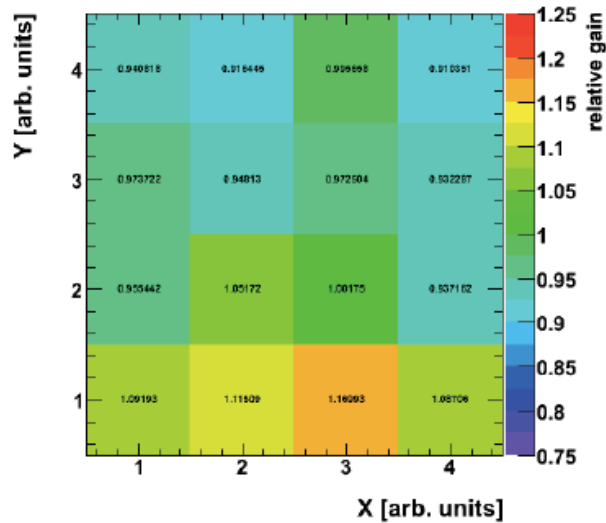


# FGT Technical realization

## □ Source tests (2)



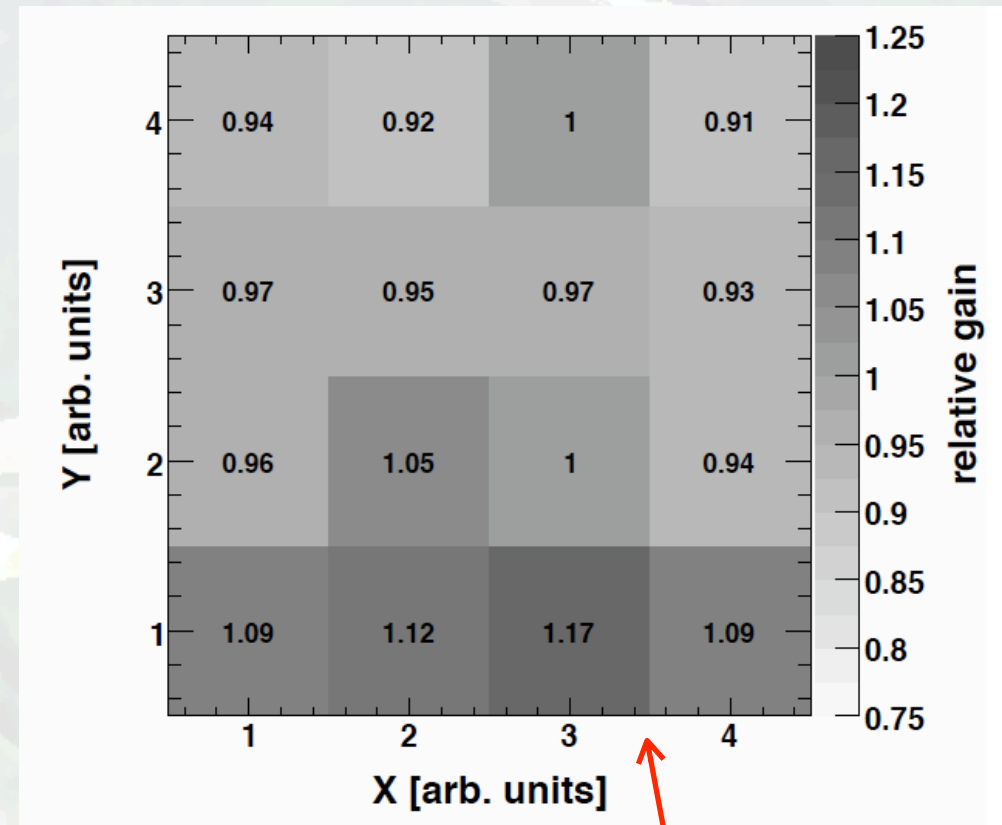
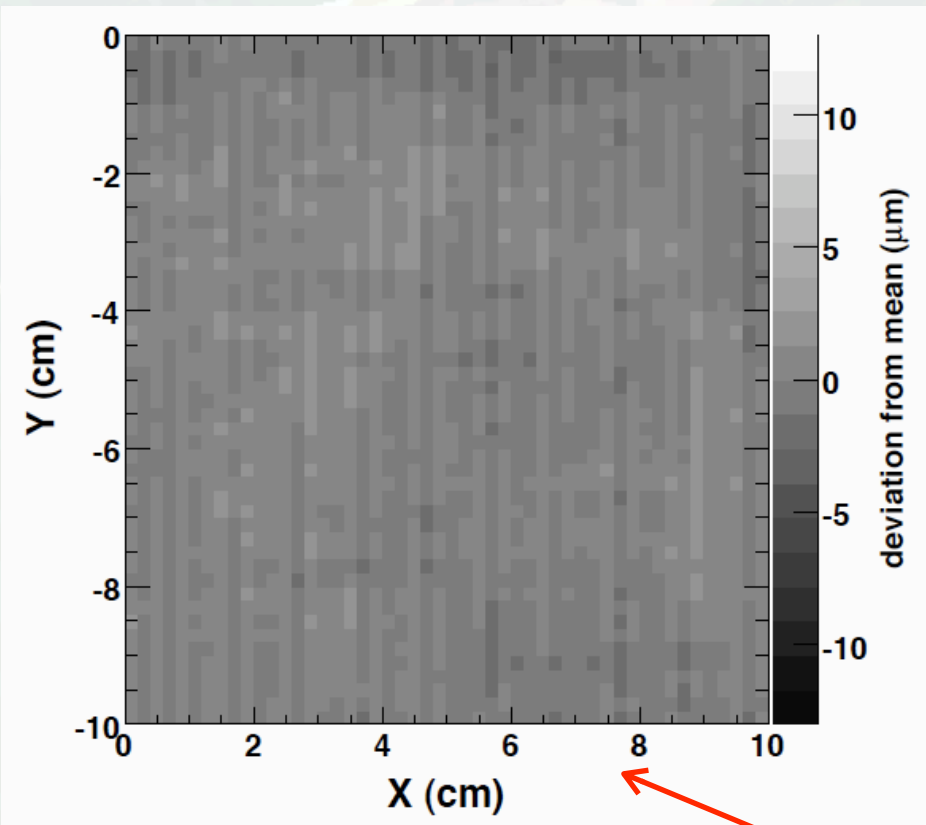
- Gain measured with low intensity  $^{55}\text{Fe}$  source ( $\sim 0.5\text{Hz}/\text{mm}^2$ )



- Good gain uniformity over full active area (Measured after charge built-up)

# FGT Technical realization

## □ Source tests (3)

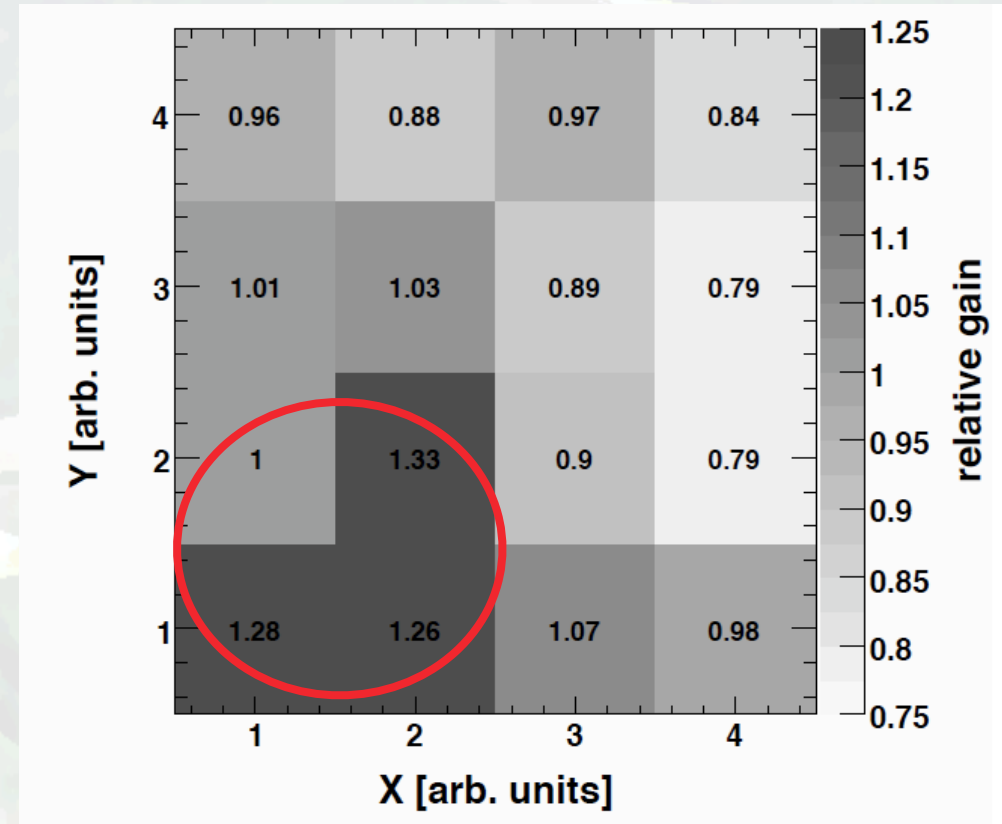
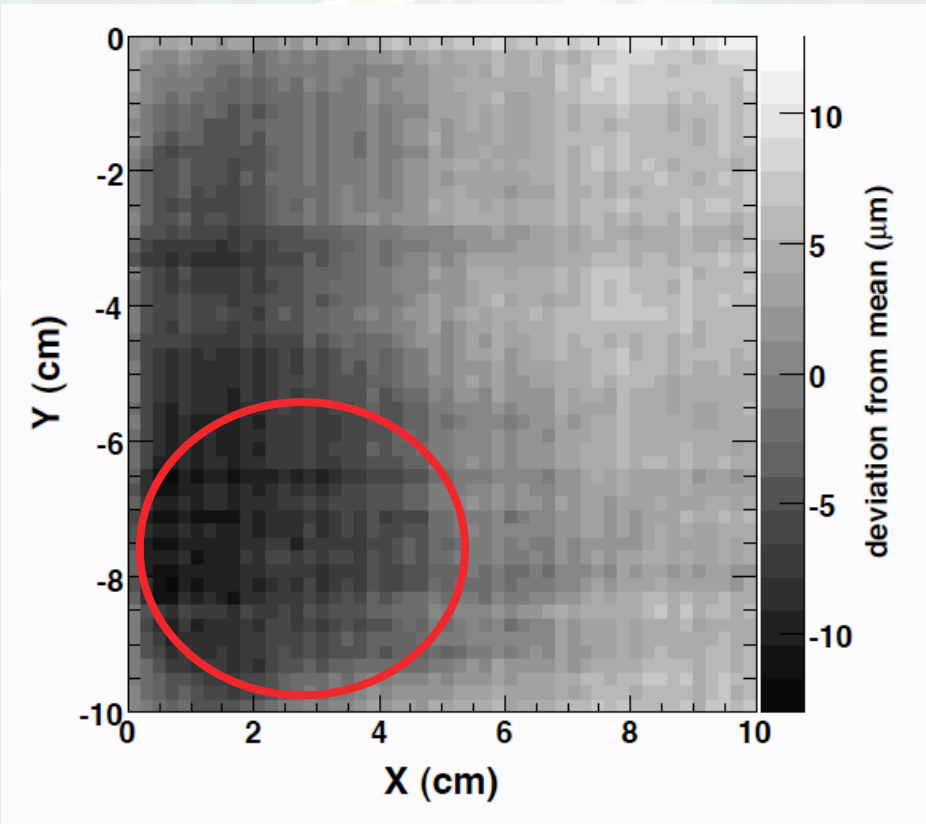


○ Comparison of optical scans of inner hole diameter uniformity and gain uniformity

from low-intensity  $^{55}\text{Fe}$  source ( $\sim 0.5\text{Hz}/\text{mm}^2$ ) measurements

# FGT Technical realization

## □ Source tests (4)



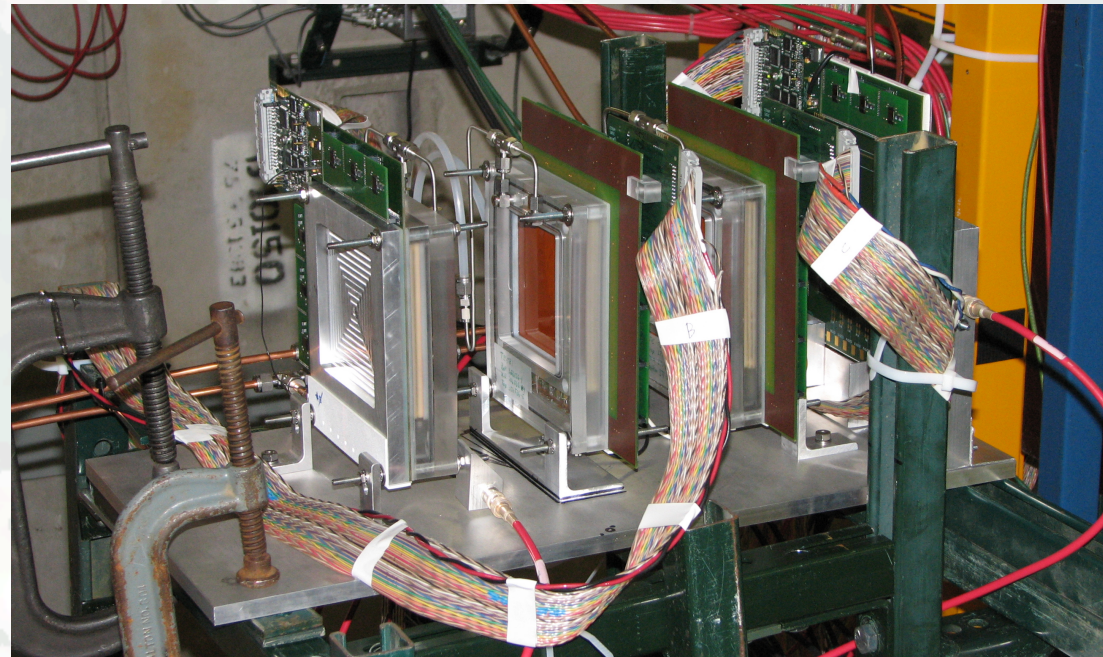
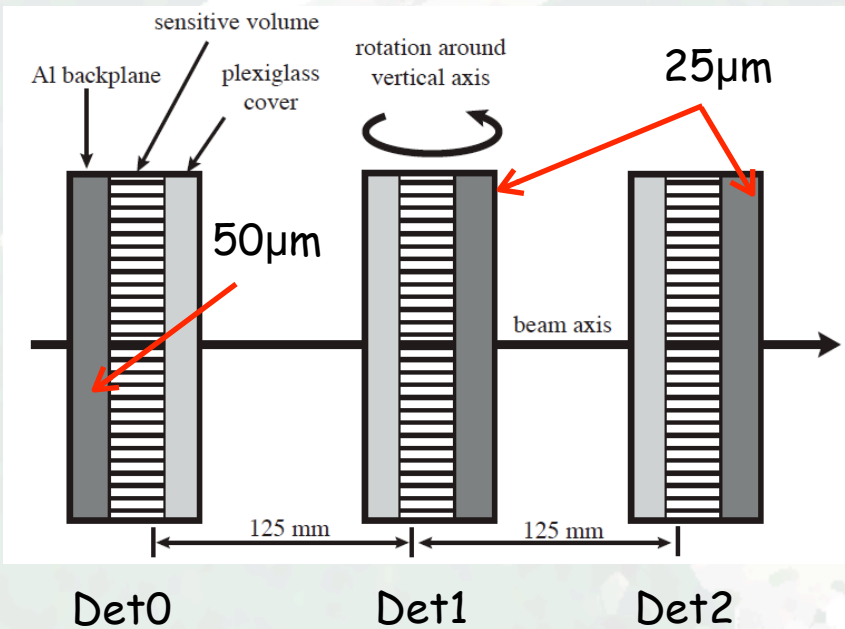
○ Non-uniformity of inner hole diameter ( $\sim 20\mu\text{m}$  smaller on left side compared to right side)

reflected in large non-uniformity of source scan gain measurements



# FGT Technical realization

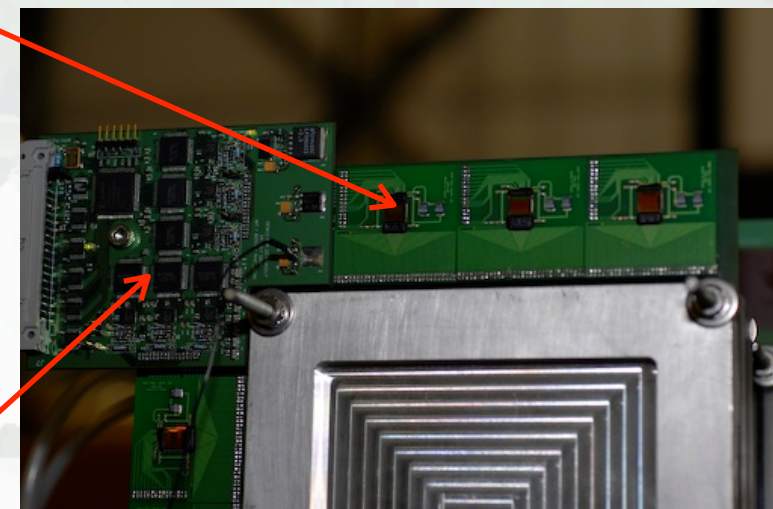
## Testbeam results (1)



APV25-S1

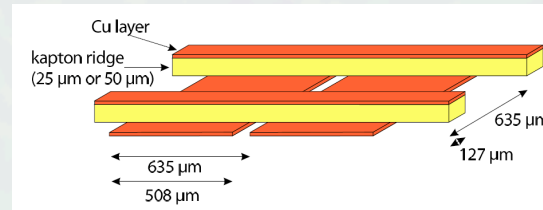
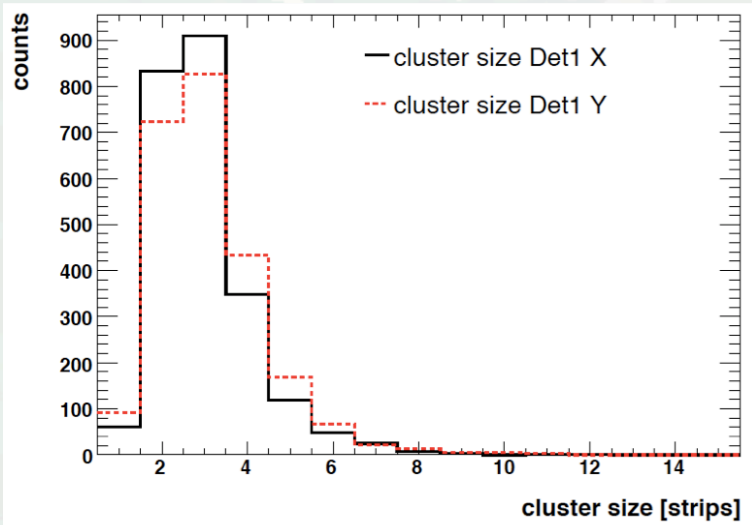
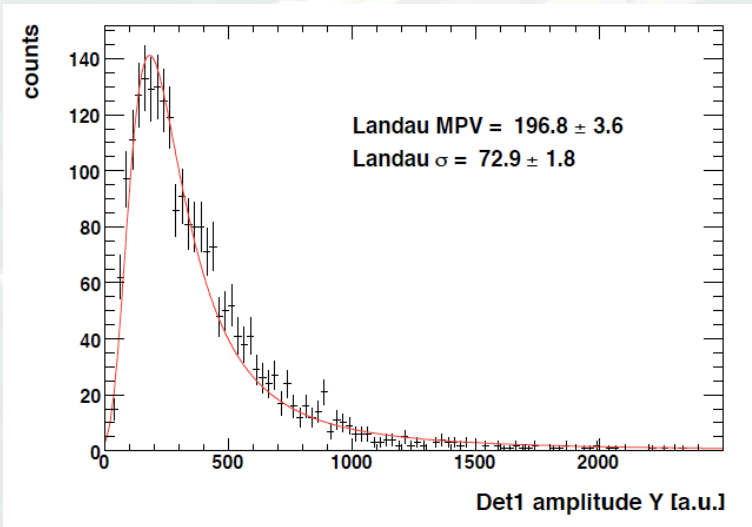
- FNAL Meson Test Beam Facility: Data taking with 4GeV-32GeV unseparated secondary beam and 120GeV primary proton beam

FPGA Readout System



# FGT Technical realization

## □ Testbeam results (2)

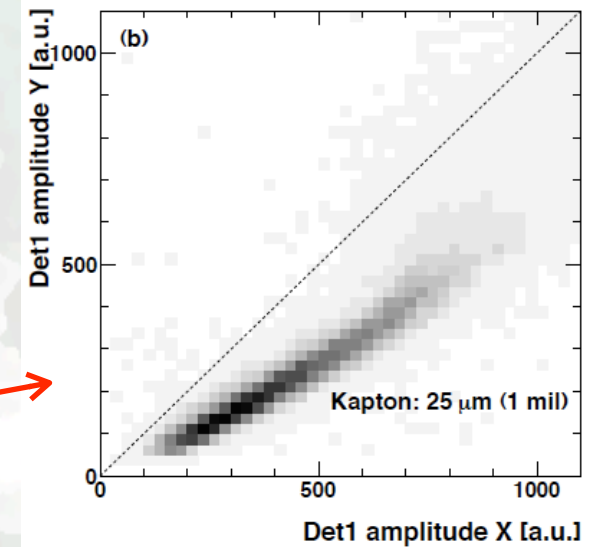
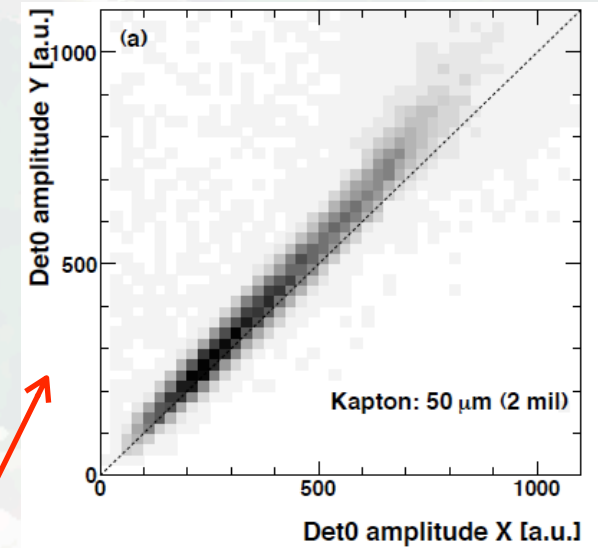


### ○ Cluster charge

follows expected  
distribution

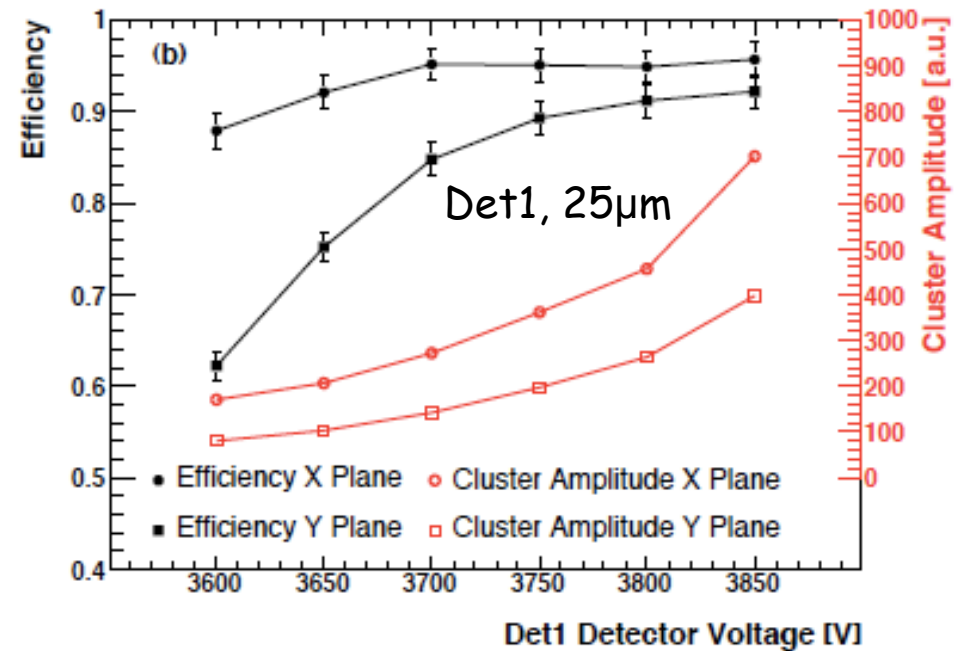
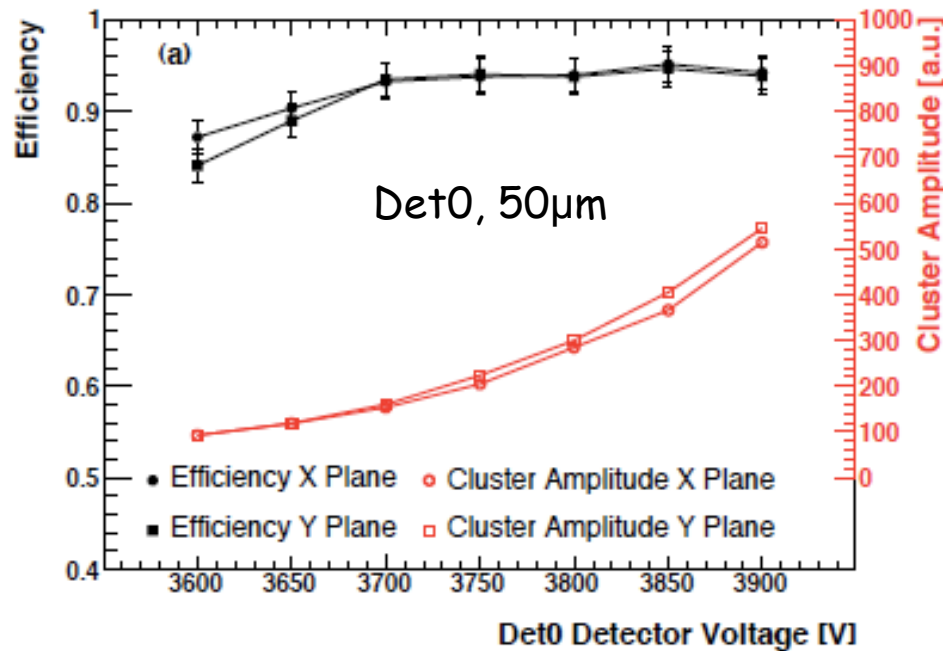
### ○ Two version of readout board

(50 $\mu\text{m}$   
and 25 $\mu\text{m}$ )



# FGT Technical realization

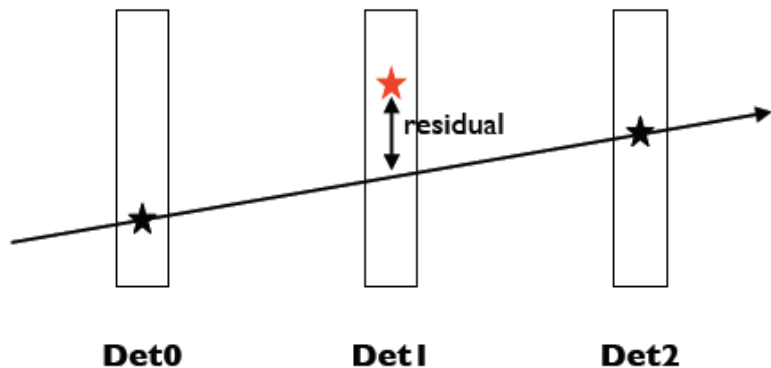
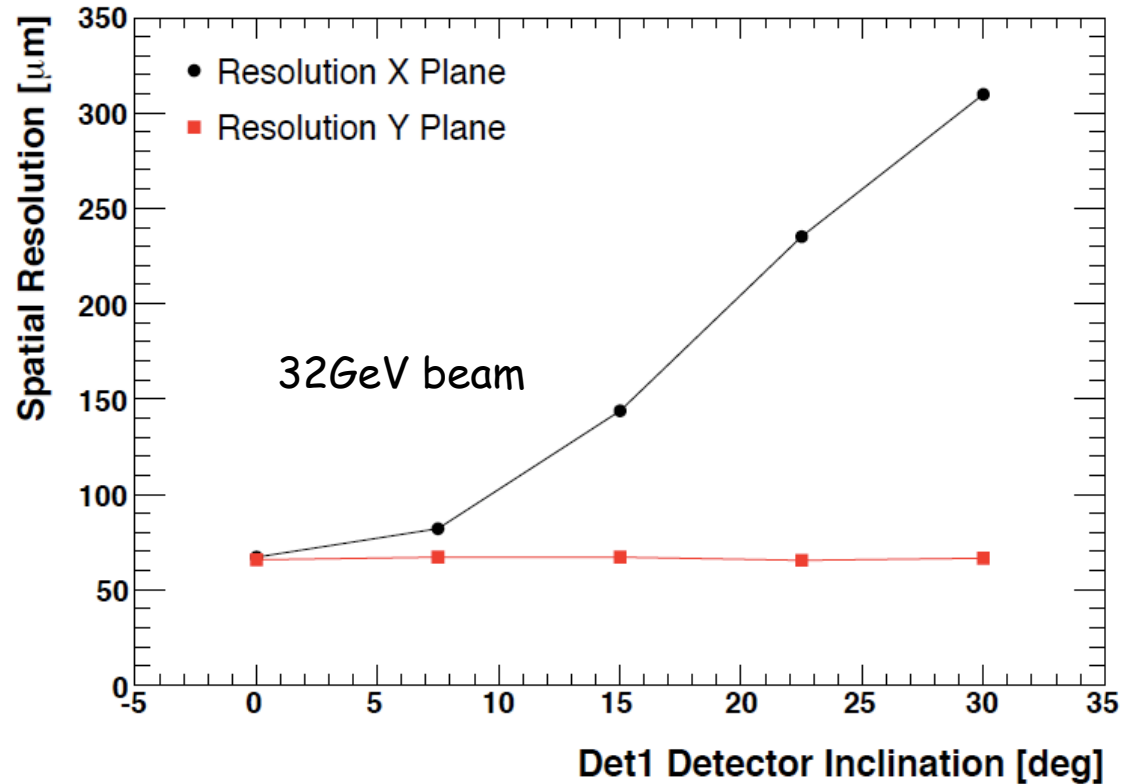
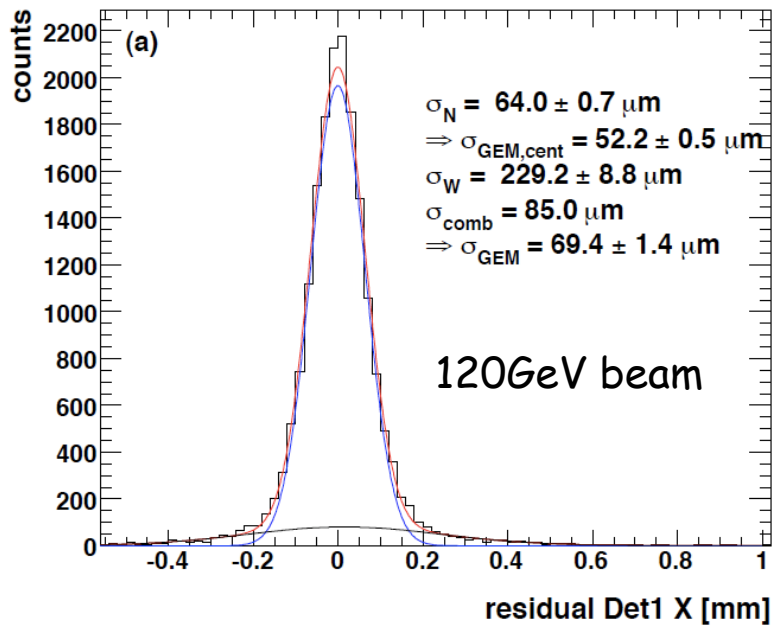
## Testbeam results (3)



- Efficiencies at the level of ~95%-98% were reached in regions which limit the impact of noisy and dead regions with Tech-Etch GEM foils (Not affected by high intensity studies)
- Clear difference between Det0 (50 $\mu$ m) and Det 1 (25 $\mu$ m) for efficiency and cluster amplitude (Most probable value of Landau distribution)

# FGT Technical realization

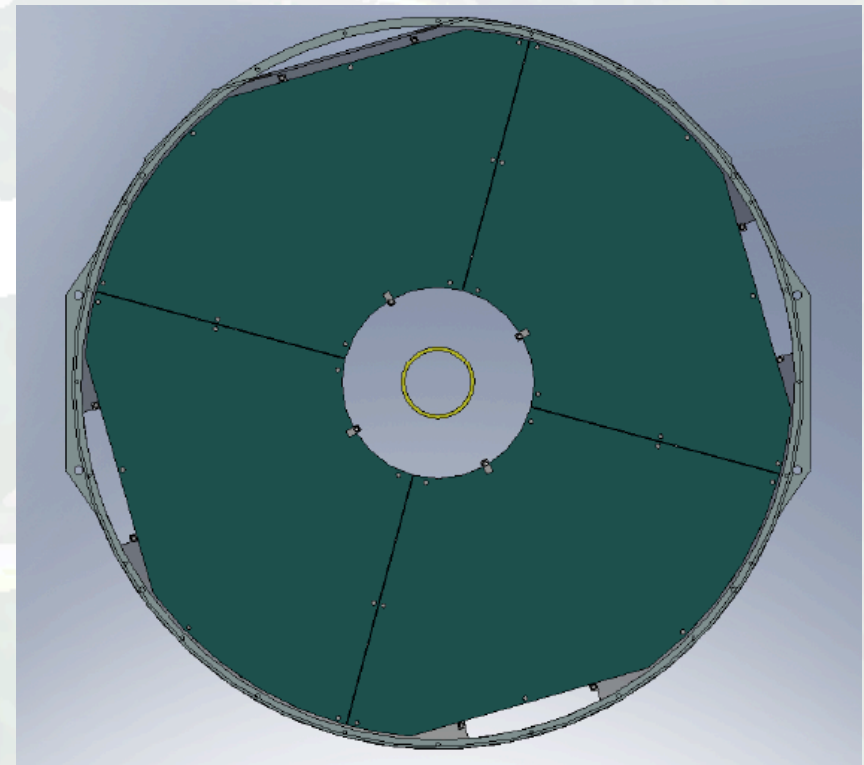
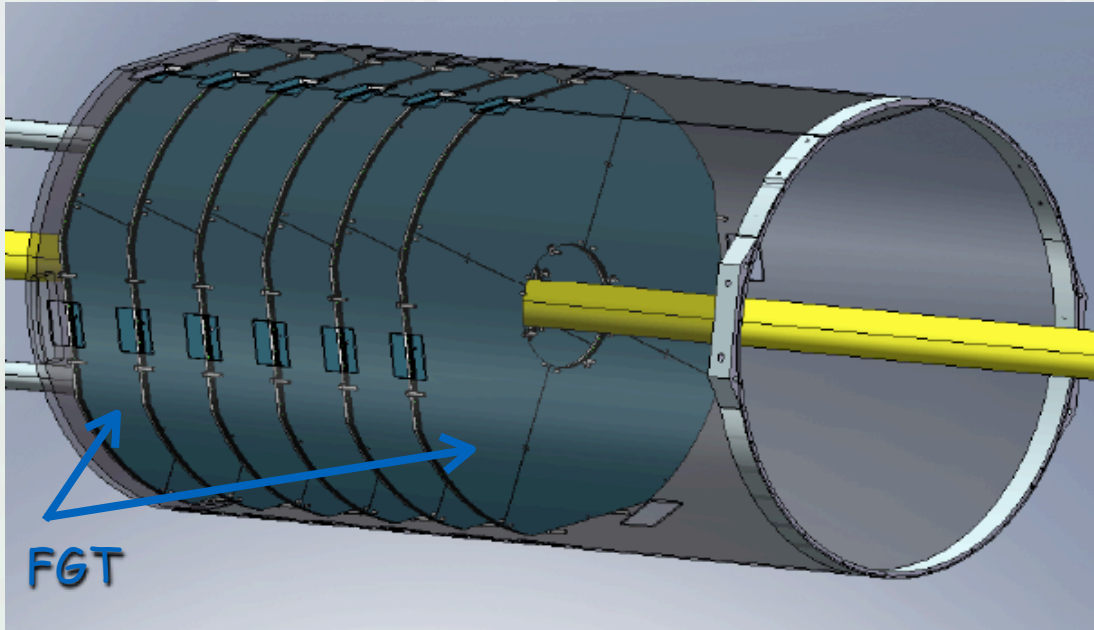
## □ Testbeam results (4)



- Study of inclination by up to  $30^\circ$ : Only X (horizontal) resolution is affected, not so for Y (vertical) coordinate as expected!

# FGT Technical realization

## □ Layout

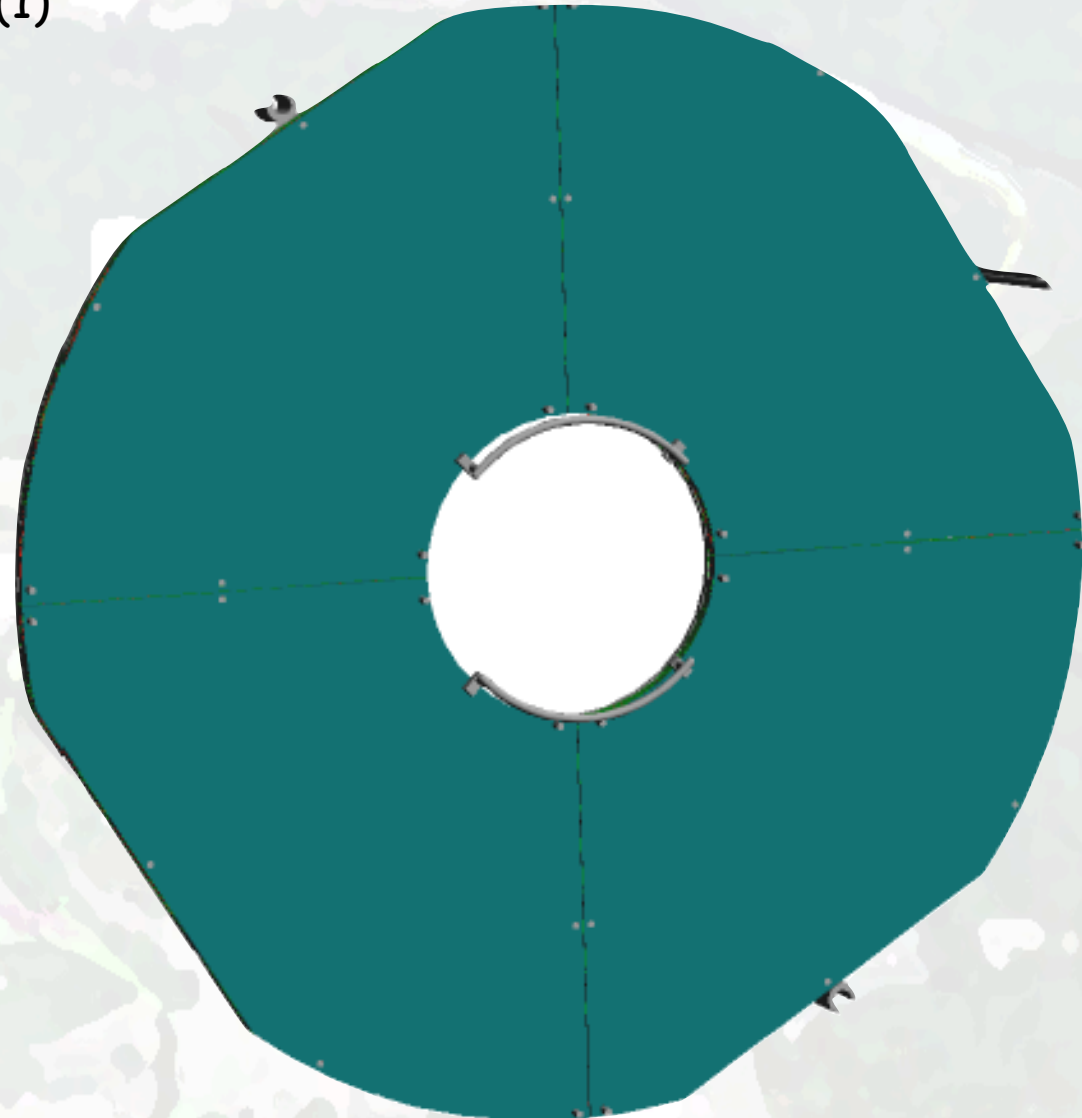


- FGT: 6 light-weight disks
- Each disk consists of 4 triple-GEM chambers (Quarter sections)
- Procurement and assembly of full quarter section prototype in preparation

# FGT Technical realization

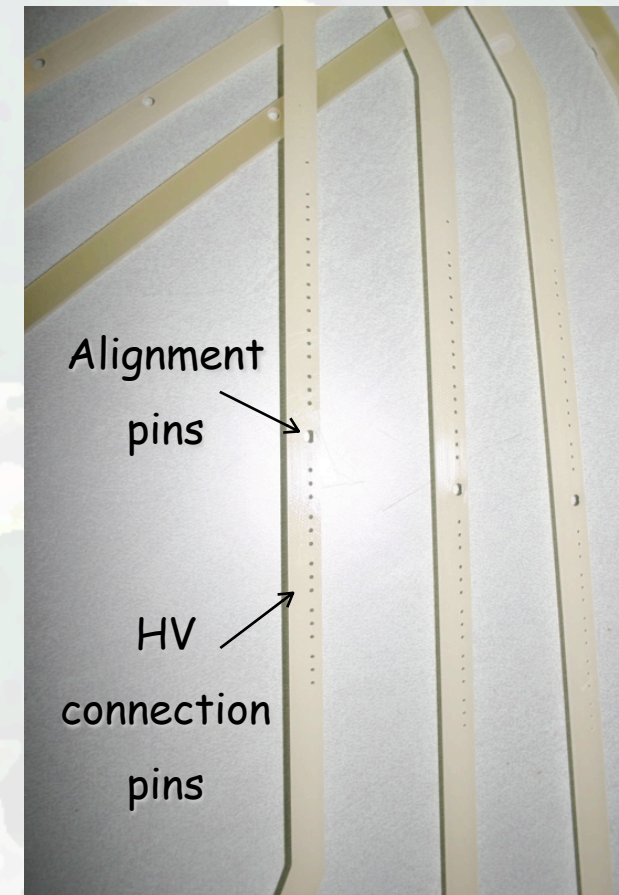
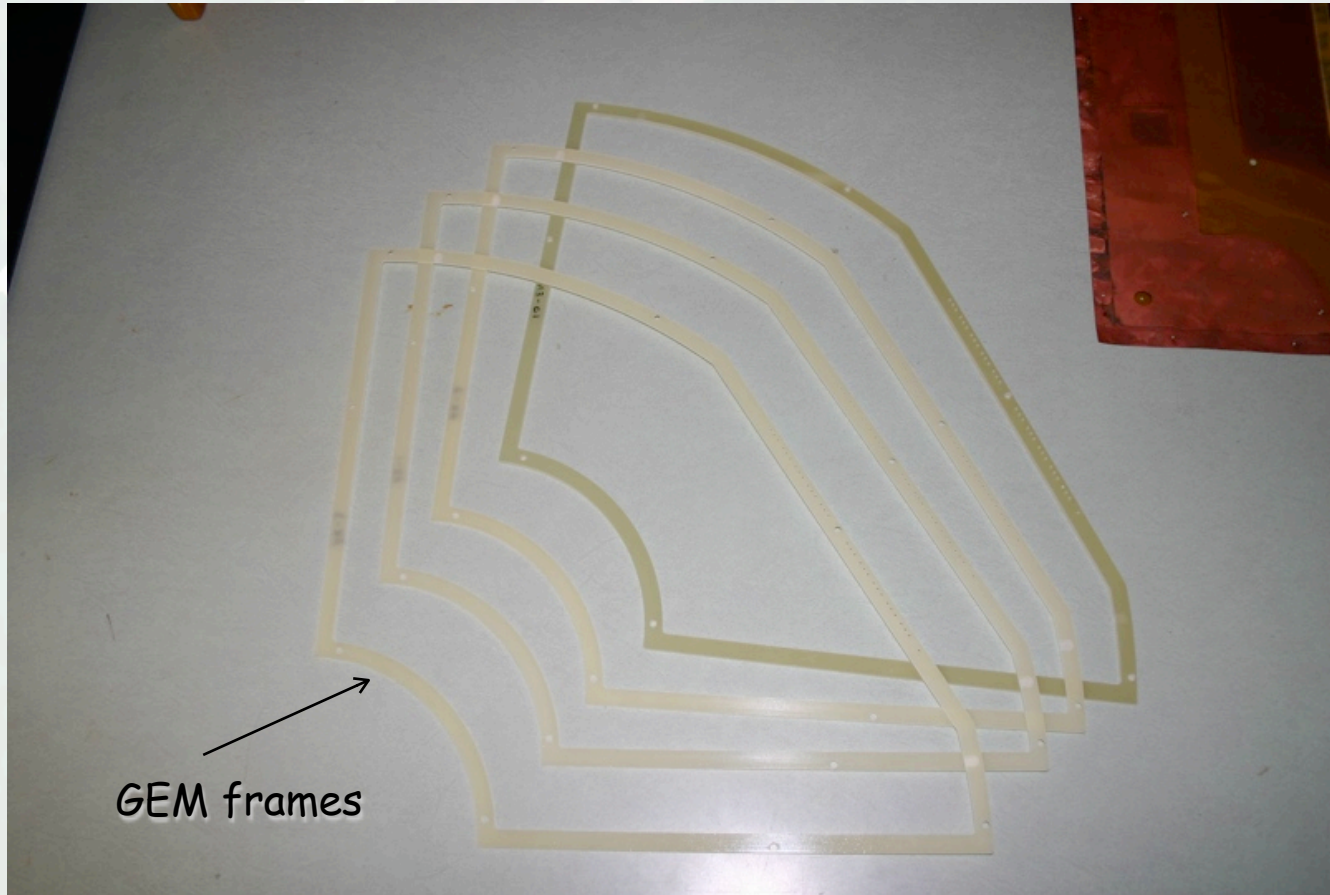
## □ Triple-GEM: Quarter section design (1)

- Single disk
  - 5mm Nomex honeycomb
  - 0.25mm FR4 skins
  - Pins used as part of assembly and alignment
- GEM quadrant
  - Pins define position
  - Pins preserve shape
- Gas manifolds and rails



# FGT Technical realization

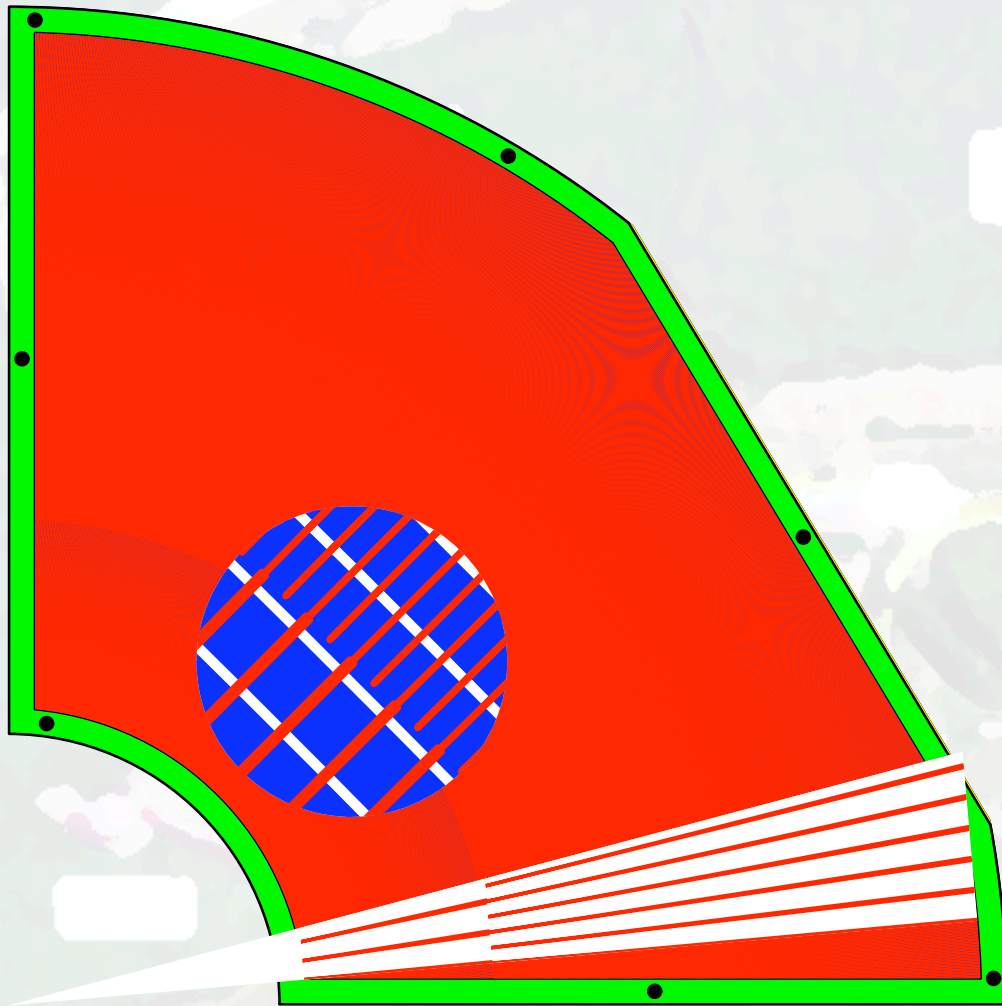
## □ Triple-GEM: Quarter section design (2)



- Dimensions close to final design (WSC dimensions)
- Verify mechanical detail
- Develop stretching and assembly fixtures / Test flatness of GEM foils

# FGT Technical realization

## □ Triple-GEM: Quarter section design (3)



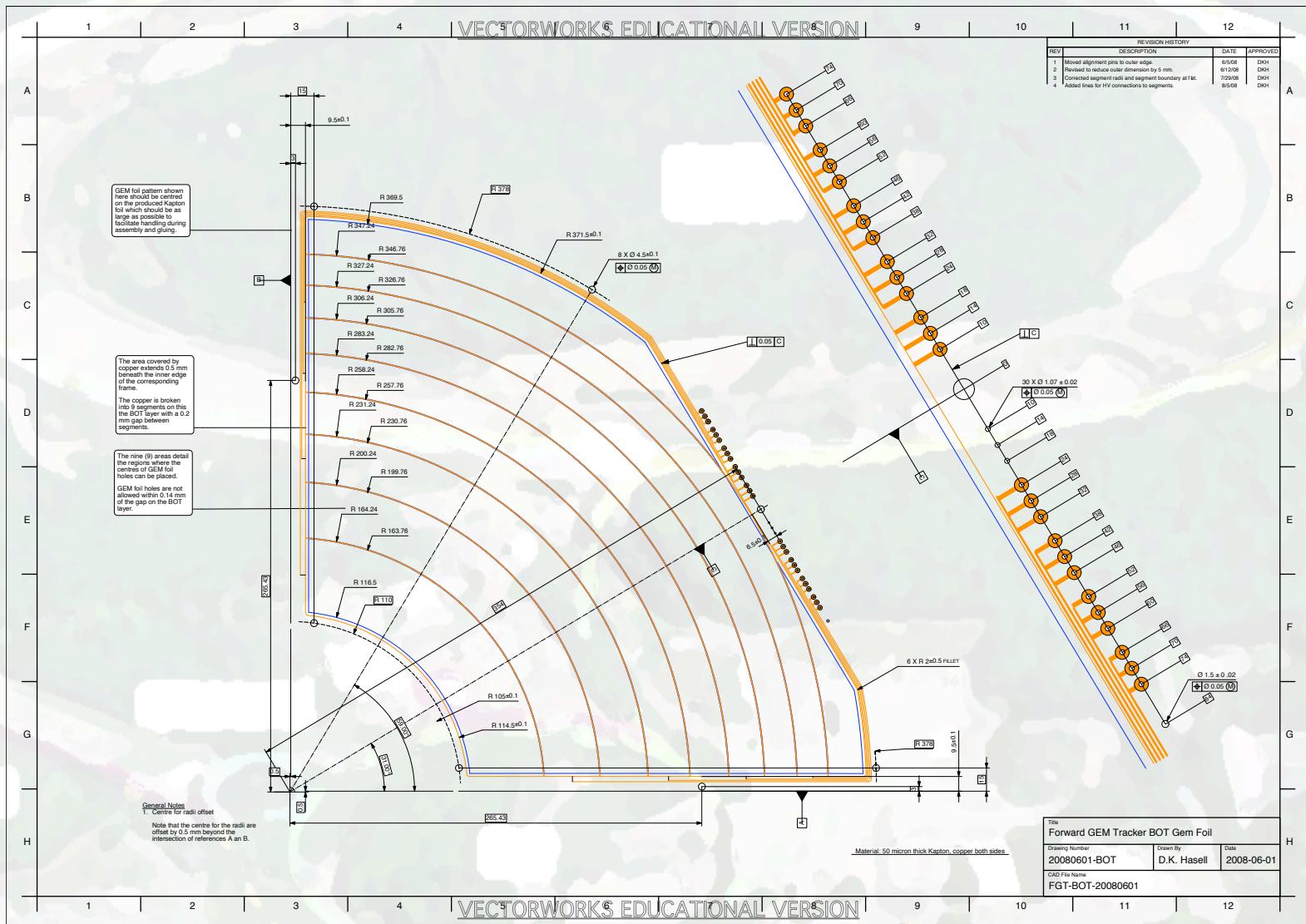
- 50  $\mu\text{m}$  Kapton
- Copper on both sides
- Laser etching exposes bottom layer
- Top layer
  - $\Phi$ -readout layer
  - Alternate lines end at 18.8cm
  - Pitch: 300-600  $\mu\text{m}$
  - Line width: 80-120 $\mu\text{m}$
- Bottom layer
  - R-readout layer
  - Pitch: 800 $\mu\text{m}$
  - Line width: 700 $\mu\text{m}$





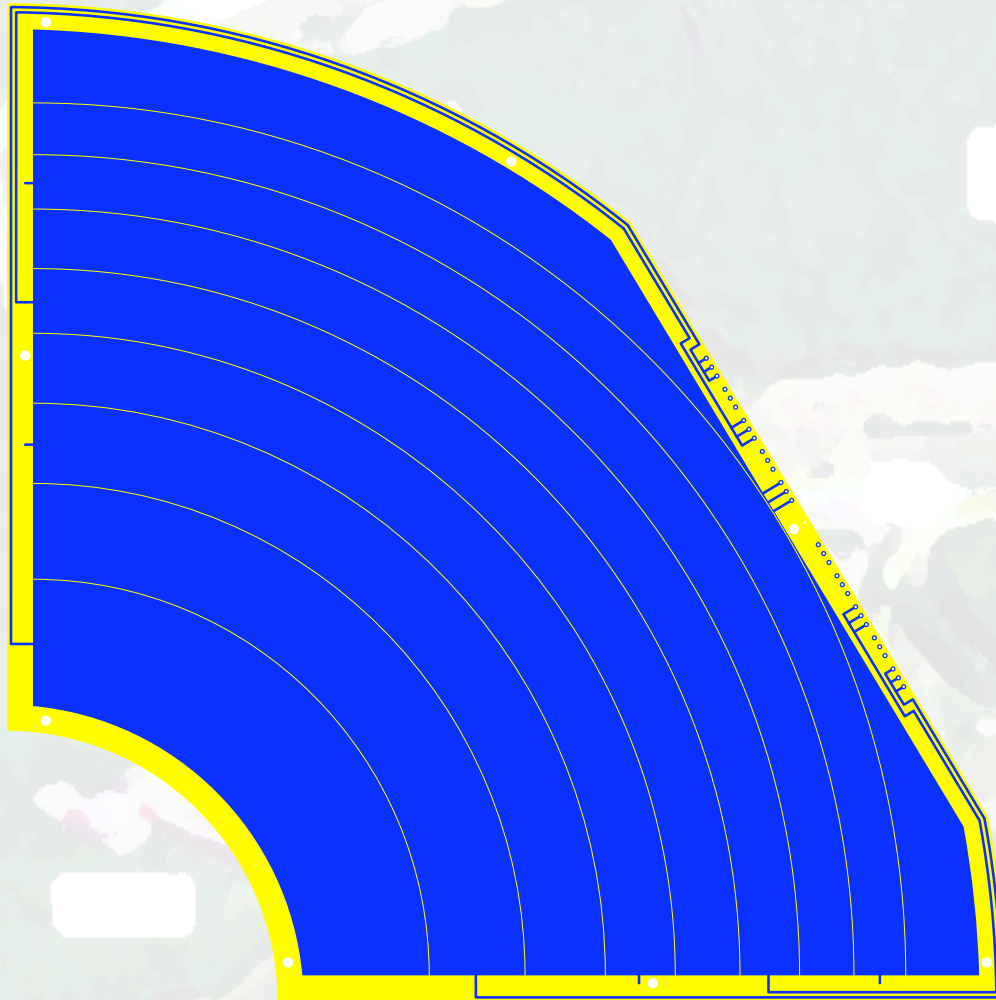
# FGT Technical realization

## Triple-GEM: GEM foil design (1)



# FGT Technical realization

## □ Triple-GEM: GEM foil design (2)

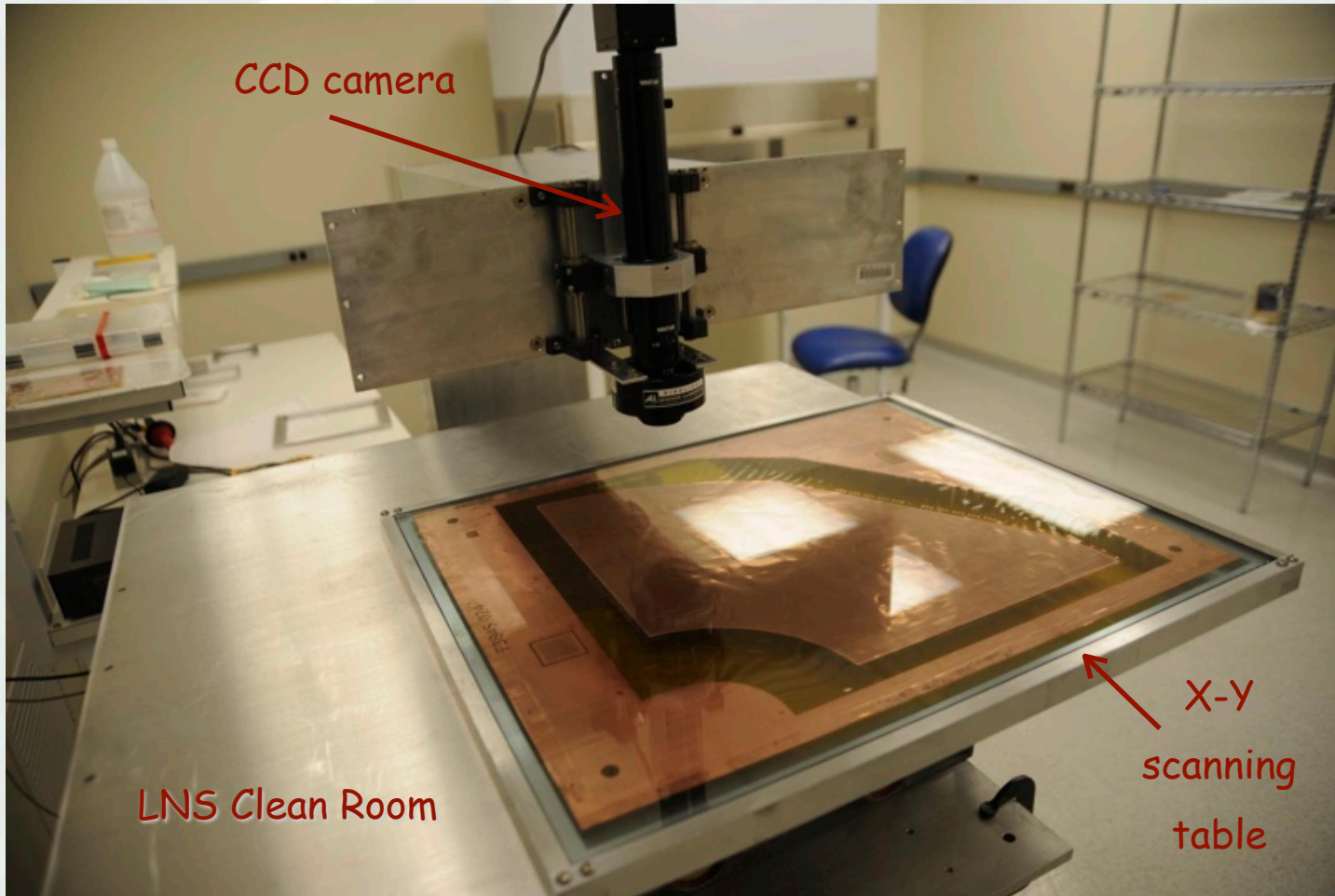


### Segmented GEM foils:

- Minimize damage in case of breakdown
- 9 segments in radial direction with  $\sim 100\text{cm}^2$  each
- Gap:  $200\mu\text{m}$
- Hole pitch ( $\sim 140\mu\text{m}$ ) and diameter (I:  $\sim 50\mu\text{m}$  / O:  $\sim 60\mu\text{m}$ ) similar to prototype!
- Routing and vias distribute HV to segments

# FGT Technical realization

## □ Triple-GEM: GEM foil testing (1)



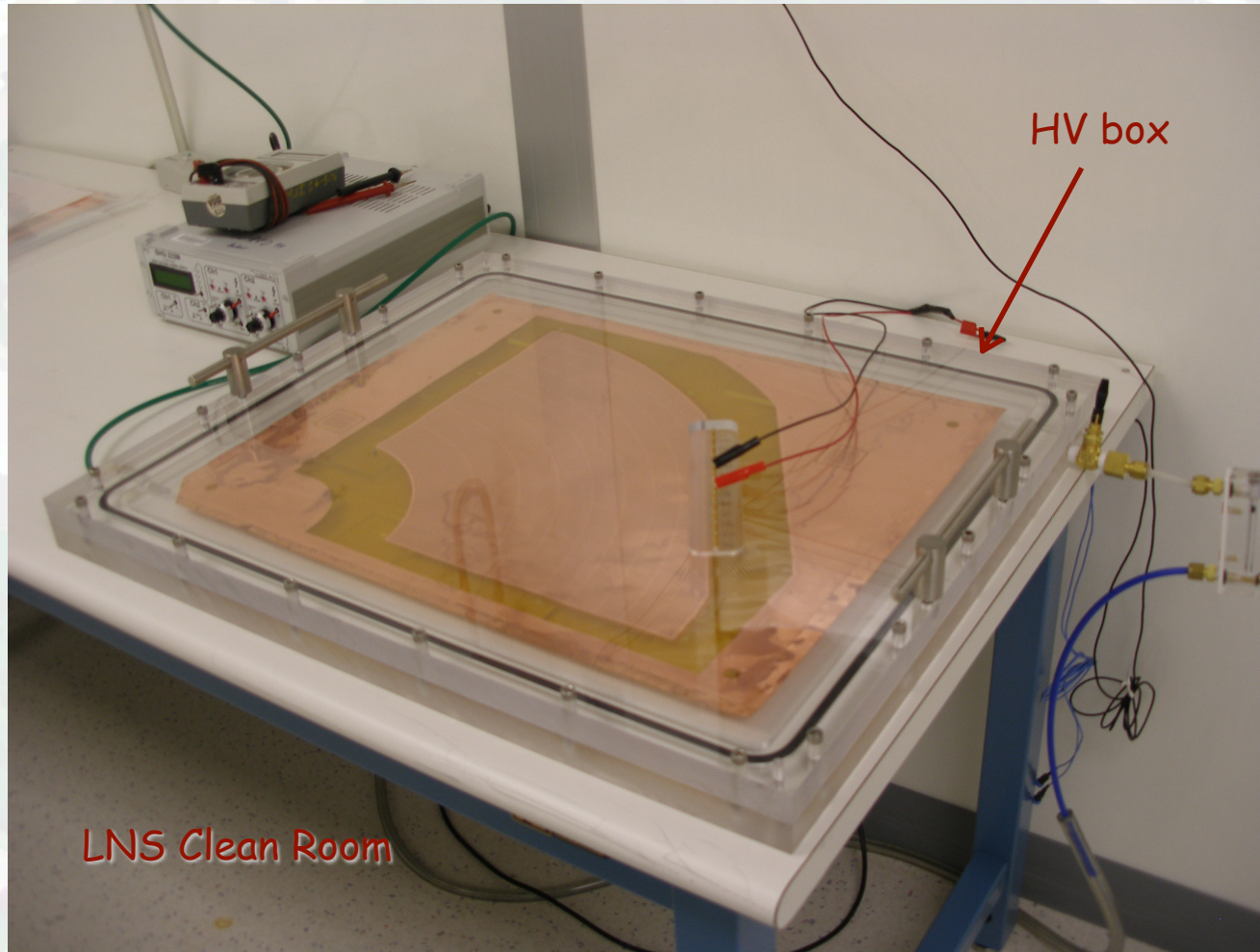
### Optical scans:

- Measure inner and outer hole diameter / Uniformity across full surface (Important for gain uniformity) - Ongoing
- Systematic Tech-Etch and CERN comparison

CCD camera setup for optical GEM foil scans

# FGT Technical realization

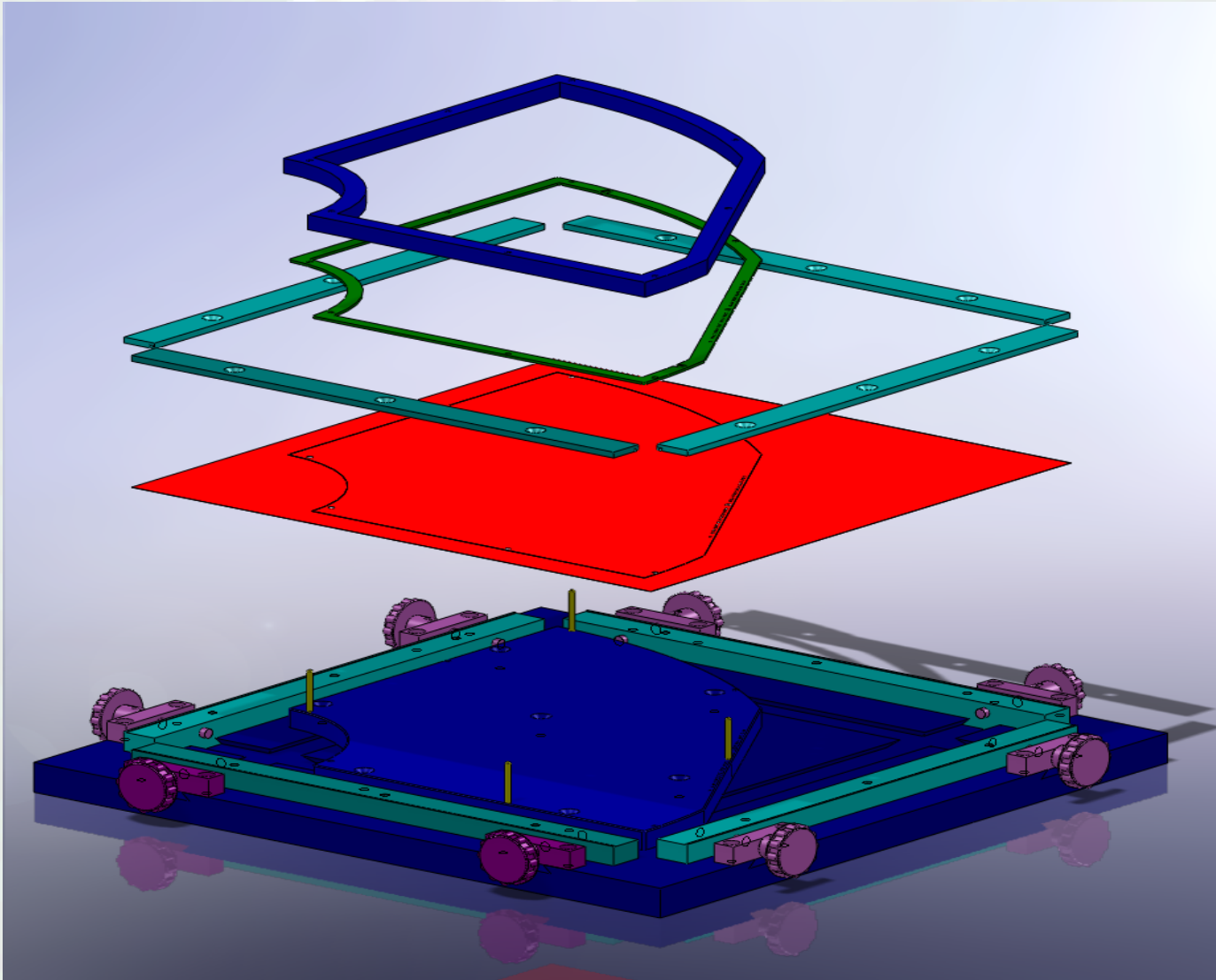
## □ Triple-GEM: GEM foil testing (2)



HV box for GEM foil dark current tests

# FGT Technical realization

## □ Triple-GEM: GEM foil stretching and assembly tooling



### Stretching jig:

- Stretch GEM foil
- Clamp 2mm spacer for single glue operation

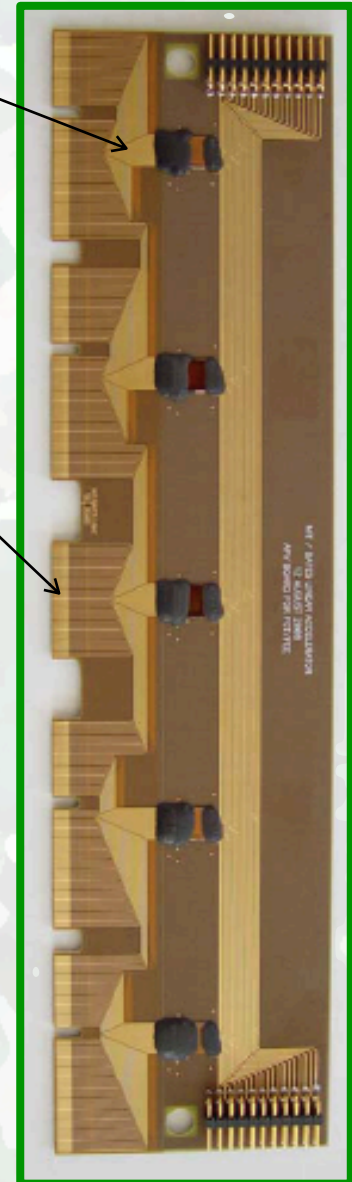
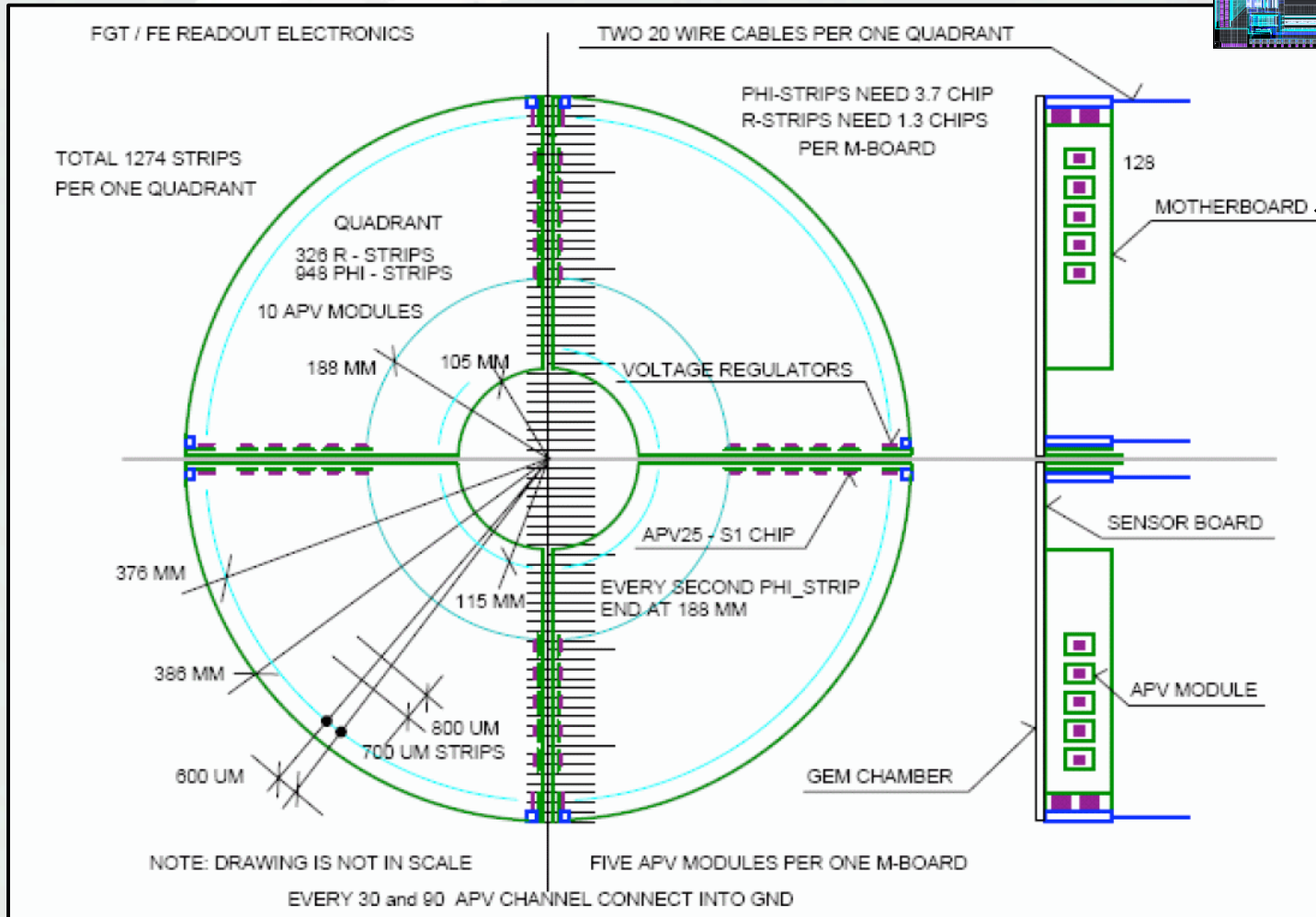
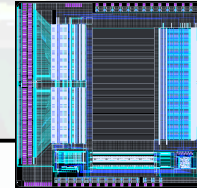
### Assembly jig:

- Align frames to each other and to SIMM pins
- Hold frames flat with clamps
- Hold SIMM pins in place for soldering
- Clamp frames together for gluing operation

# FGT Technical realization

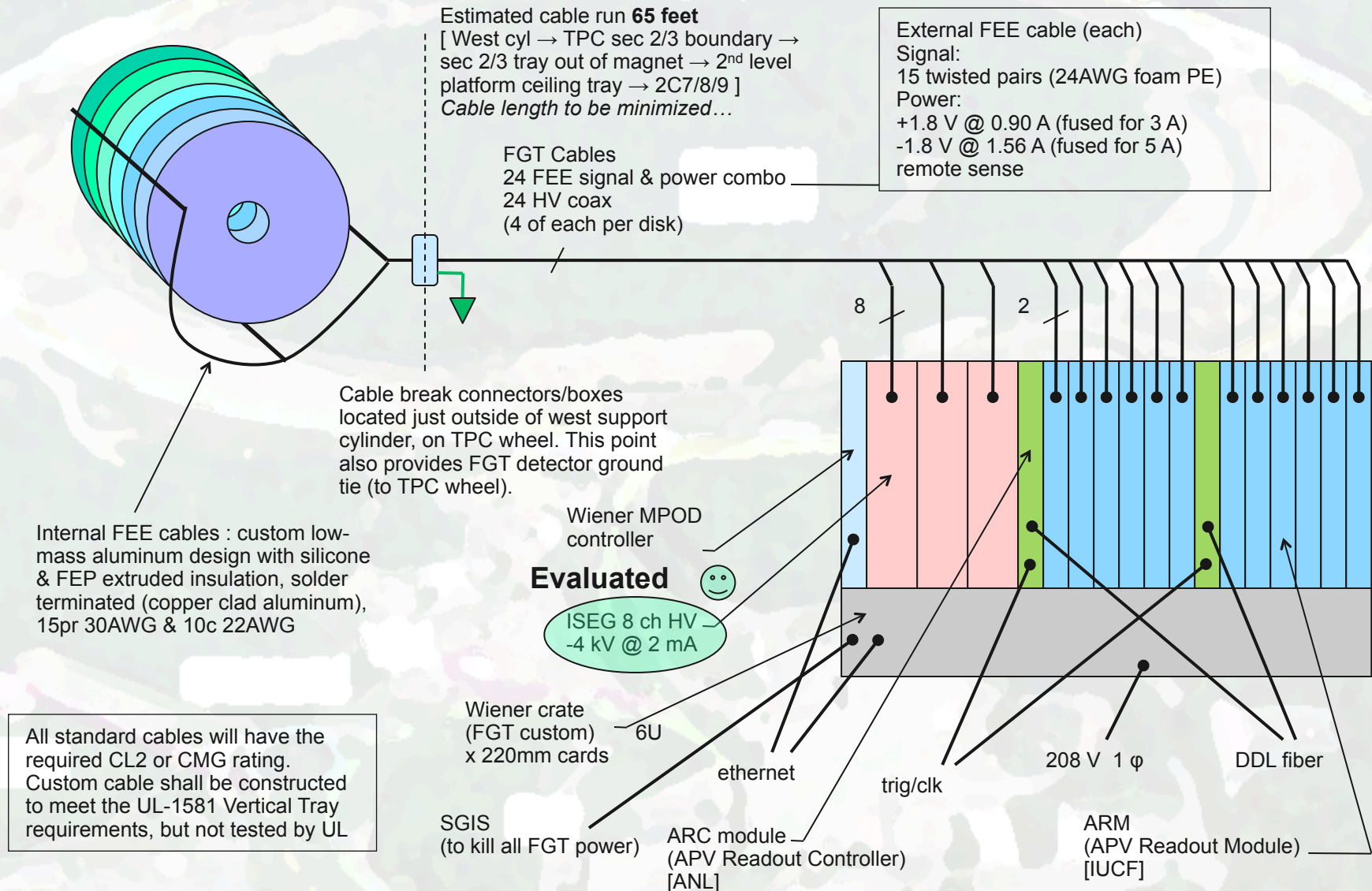
## □ FEE: Overview

APV25-S1 chips



# FGT Technical realization

## □ DAQ: Overview



# Summary

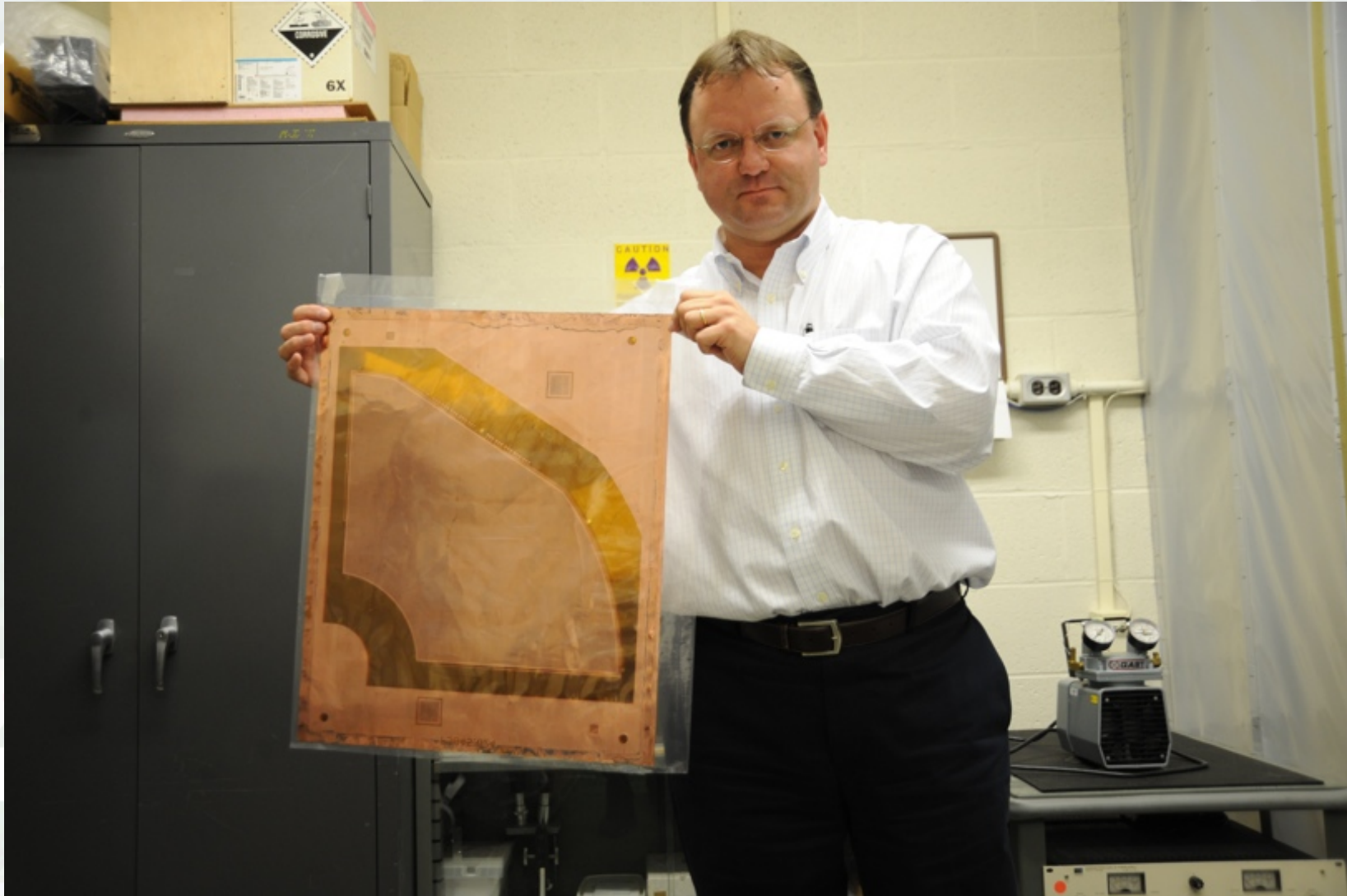
## □ Milestones / Schedule

- **Goal:** Complete FGT construction in ~fall 2010 followed by full system test and subsequent full installation in ~summer 2011  
⇒ Ready for anticipated first long 500GeV polarized pp run in FY12
- **Review:** Successful review January 2008 / Beginning of construction funds FY08
- **Cost estimate / planing / milestones:** R&D and pre-design work: FY07 / FY08
  - **Triple-GEM Detector:** Complete prototype tested (Bench and FNAL testbeam)
  - **Front-End Electronics (FEE) System:** Complete prototype tested / FEE design completed
  - **Data Acquisition (DAQ) System:** Layout exists based on similar DAQ sub-detector systems with extensive experience (ANL/IUCF)
  - **Mechanical pre-design completed:** Triple-GEM detector and new support structure
  - **GEM foil development:** Successful development of industrially produced GEM foils through SBIR proposal in collaboration with Tech-Etch Inc. (BNL, MIT, Yale University)



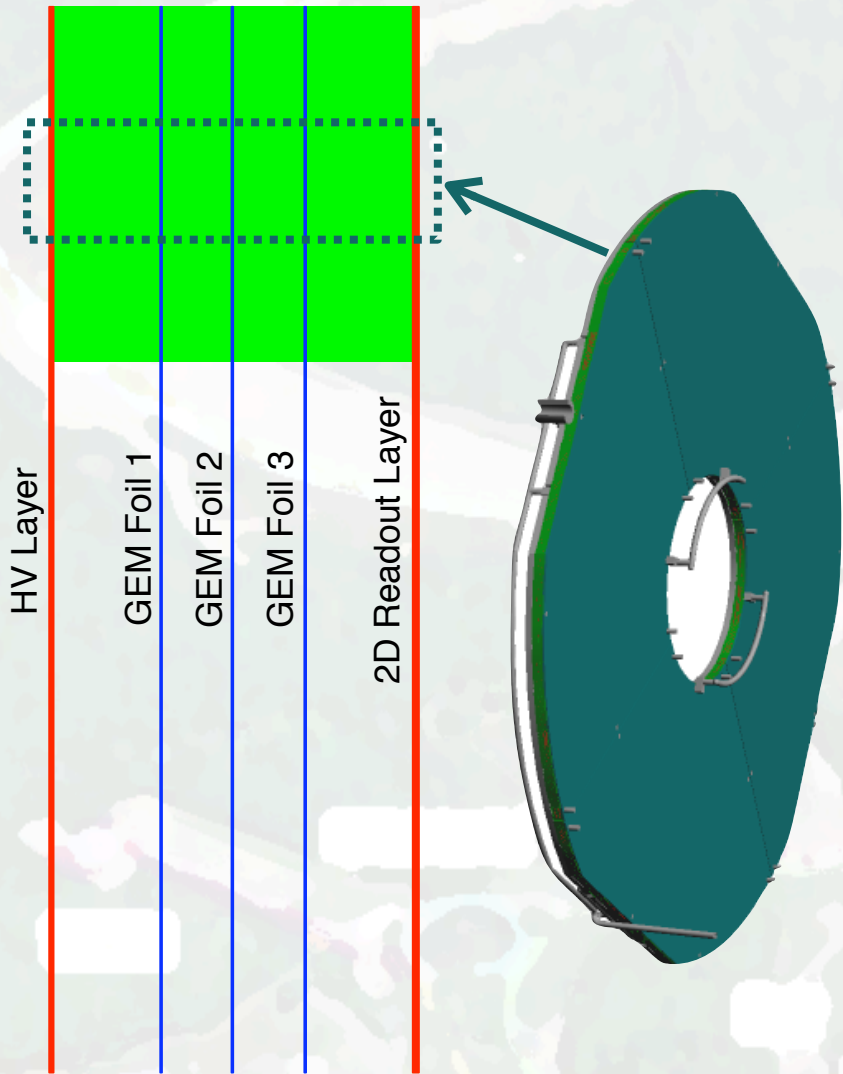
# Backup

- Triple-GEM: GEM foils at MIT



# Backup

## Triple-GEM: Quarter section design



Component	Material	Radiation Length [%]
Support plate	5 mm Nomex	0.040
	2x250 $\mu\text{m}$ FR4	0.257
HV layer	5 $\mu\text{m}$ Cu	0.035
	50 $\mu\text{m}$ Kapton	0.017
GEM foils	6x5 $\mu\text{m}$ Cu (70%)	0.147
	3x50 $\mu\text{m}$ Kapton (70%)	0.036
Readout	5 $\mu\text{m}$ Cu (20%)	0.007
	50 $\mu\text{m}$ Kapton (20%)	0.003
	5 $\mu\text{m}$ Cu (88%)	0.031
	50 $\mu\text{m}$ Kapton	0.017
	5 $\mu\text{m}$ Cu (10%)	0.004
	0.125 mm FR4	0.064
	5 $\mu\text{m}$ Cu (10%)	0.004
Drift gas	10 mm CO <sub>2</sub> (30%)	0.002
	10 mm Ar (70%)	0.006
<b>Total</b>		<b>0.670</b>



# Backup

## □ Triple-GEM: GEM foil testing (1)

### ○ HV test of GEM foils

- Verify continuity and isolation
- Measure leakage current up to 600V

### ○ Tech-Etch QA procedure: Resistance $> 10\text{GOhms}$ / Leakage current $< 5\text{nA}$ at 10% RH

### ○ MIT tests

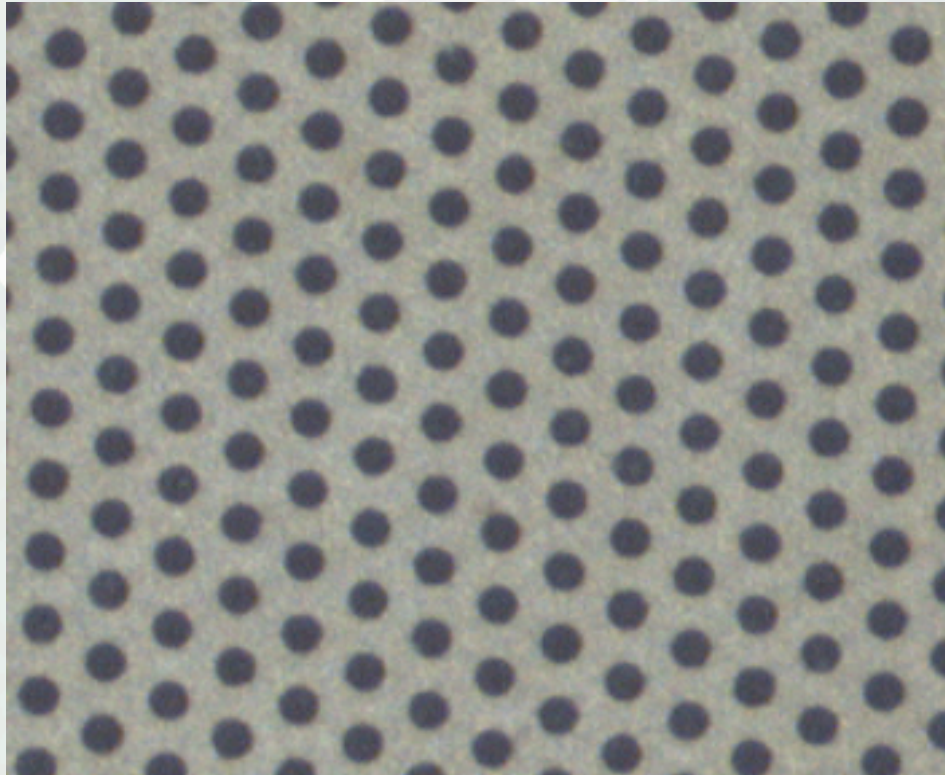
- Isolation between segments
- Quick HV test to 600V
  - Ramp HV to 100V/minute
  - Segment currents  $< 1\text{nA}$
  - Segment 8/9 problematic (Trip at 600V)
- Longer conditioning reduces leakage current, but segments 8/9 still trip at 600V

Note:

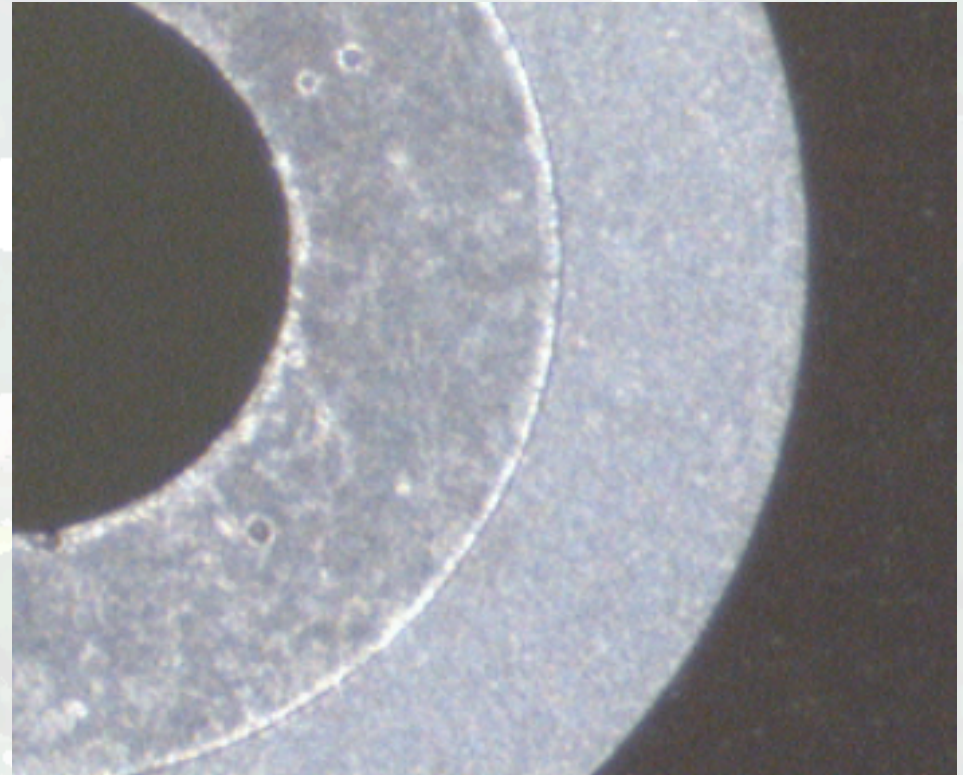
CERN production QA criteria:  
10nA max at 600V 35% Hr max

# Backup

## □ Triple-GEM: GEM foil testing (2)



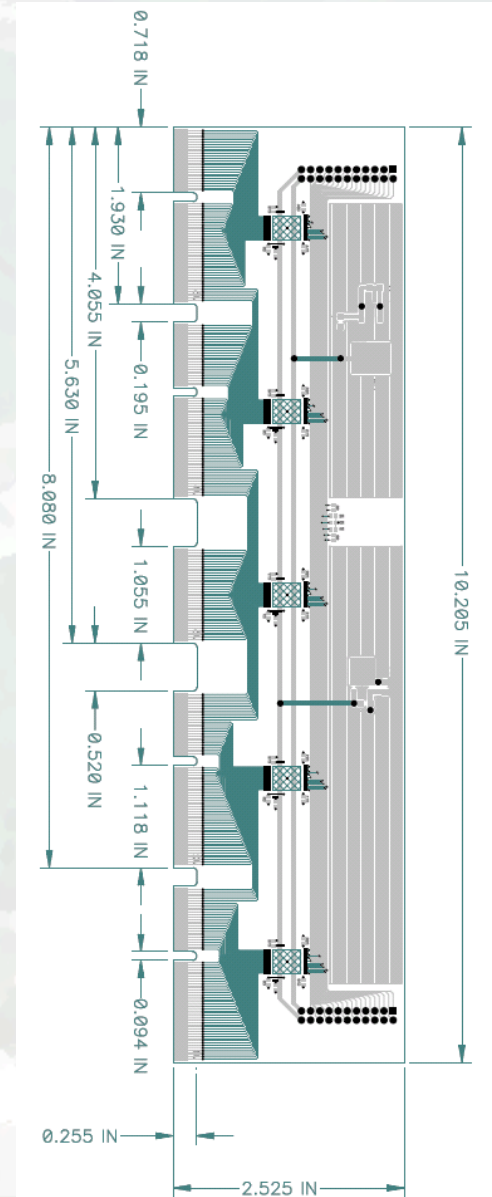
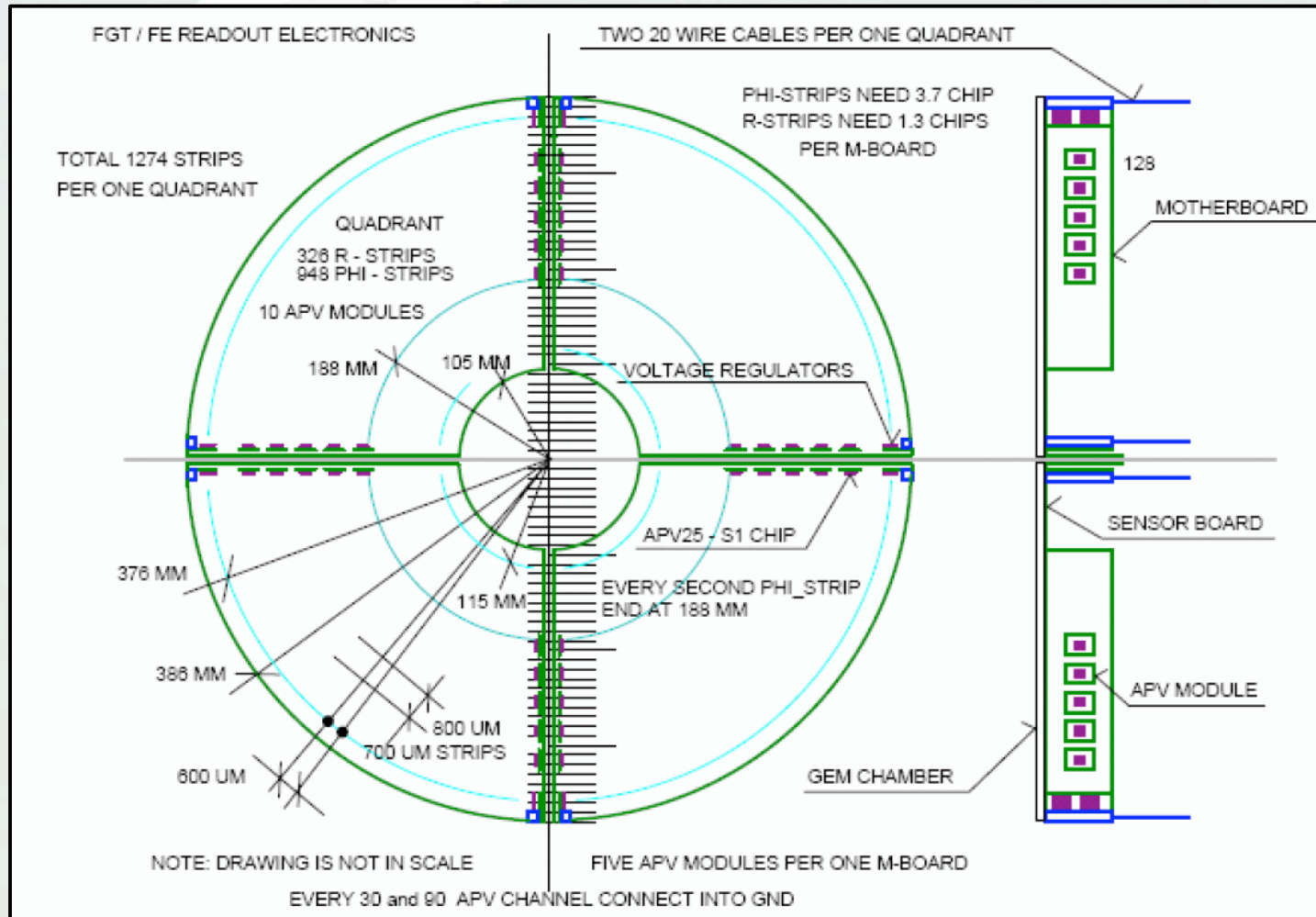
First scan for large GEM foil  
(Hole arrangement)



First scan for large GEM foil  
(HV connection)

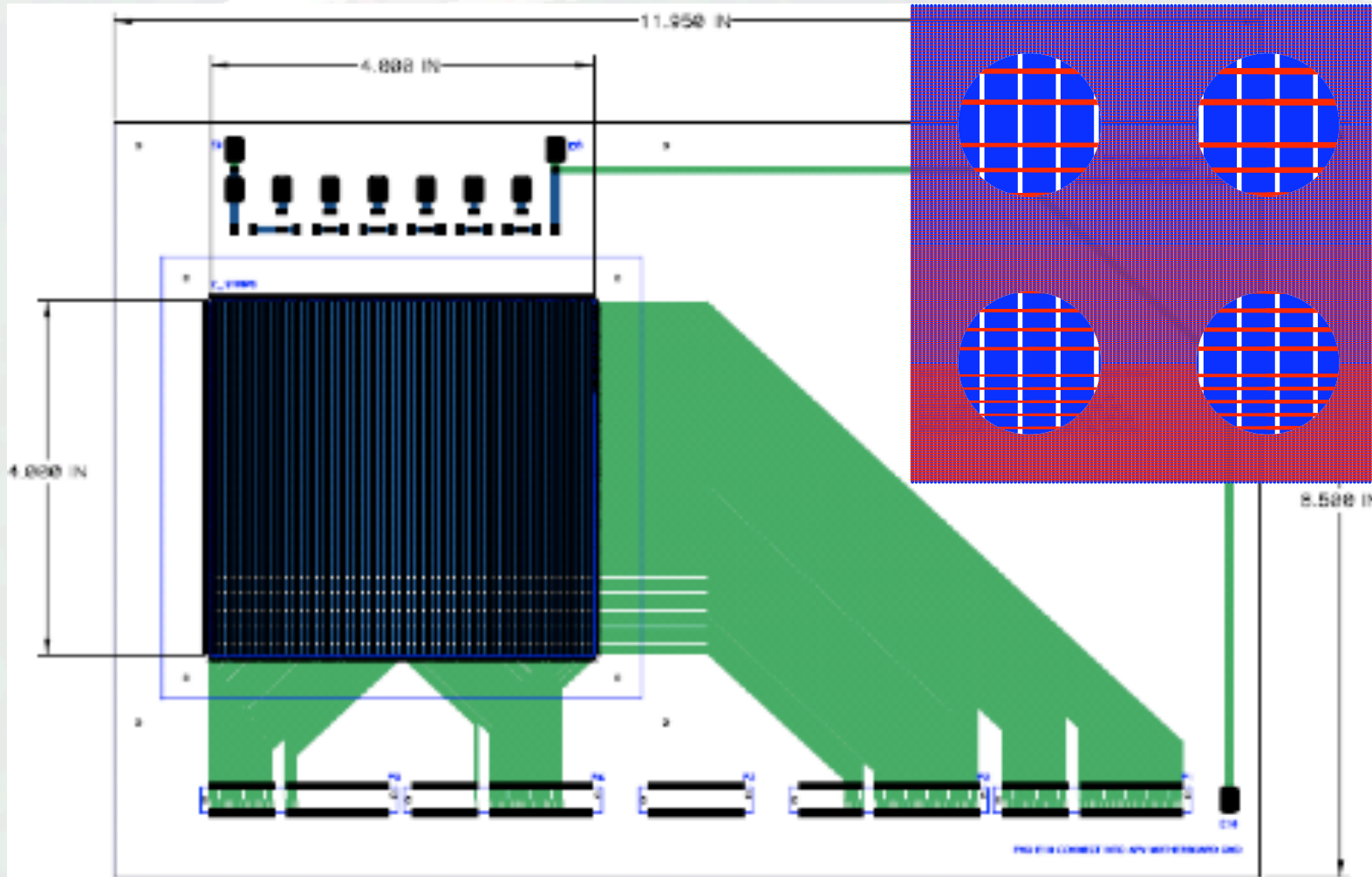
# Backup

## Triple-GEM: 2D readout board design (1)



# Backup

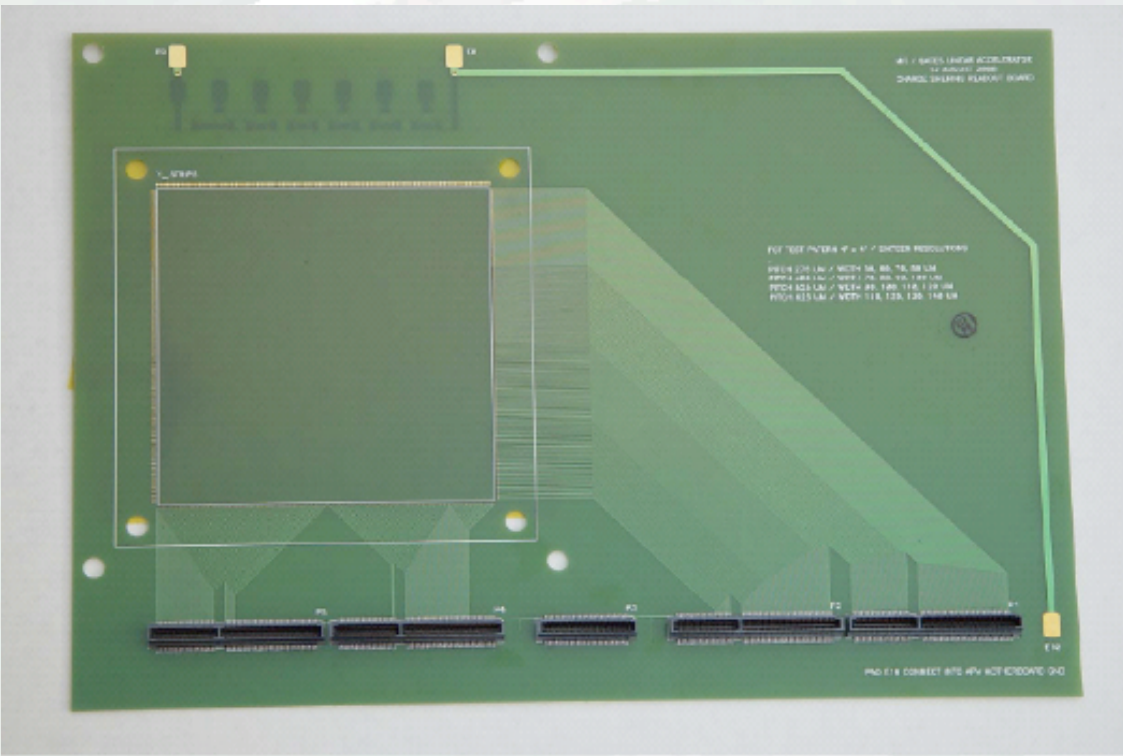
## Triple-GEM: 2D readout board design (2)



- Special 2D readout board designed (Suitable for 10 X 10 cm<sup>2</sup> prototype arrangement)
- 4 X 4 separate regions of different strip pitch/width

# Backup

## Triple-GEM: 2D readout board design (3)



- Manufactured by Compunetics Inc.
- Delivered to MIT-Bates, December 2009
- Assembly in progress using existing 10 X 10 cm<sup>2</sup> prototype
- Uniformity tests with <sup>55</sup>Fe source

Pitch [ $\mu\text{m}$ ]	Line width [ $\mu\text{m}$ ]			
650	110	120	130	140
525	90	100	110	120
400	70	80	90	100
275	50	60	70	80